



(Prof: Franco Zappa)

Electronic Systems

Possible oral questions

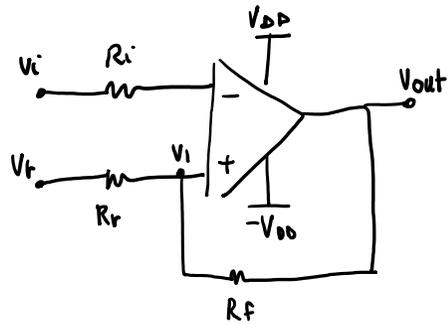
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Different OpAmp stages

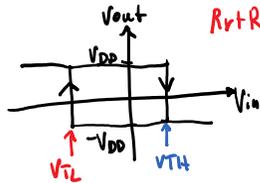
• e.g. Schmitt trigger

INVERTING

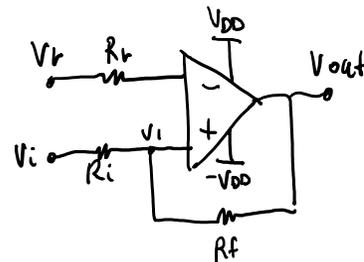


• $V_{in} < V_I \rightarrow V_{out} = V_{DD}$
 $\hookrightarrow V_I = V_{TH} = V_{DD} \frac{R_f}{R_f + R_i} + V_r \frac{R_f}{R_f + R_i}$

• $V_{in} > V_I \rightarrow V_{out} = -V_{DD}$
 $\hookrightarrow V_I = V_{TL} = -V_{DD} \frac{R_f}{R_f + R_i} + V_r \frac{R_f}{R_f + R_i}$



NON-INVERTING

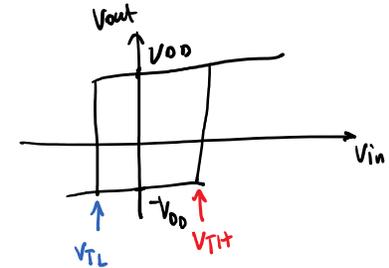


• $V_I > V_r \rightarrow V_{out} = V_{DD}$

$\hookrightarrow V_{in} = V_{TL} = \frac{R_f + R_i}{R_f} V_r - \frac{R_i}{R_f} V_{DD}$

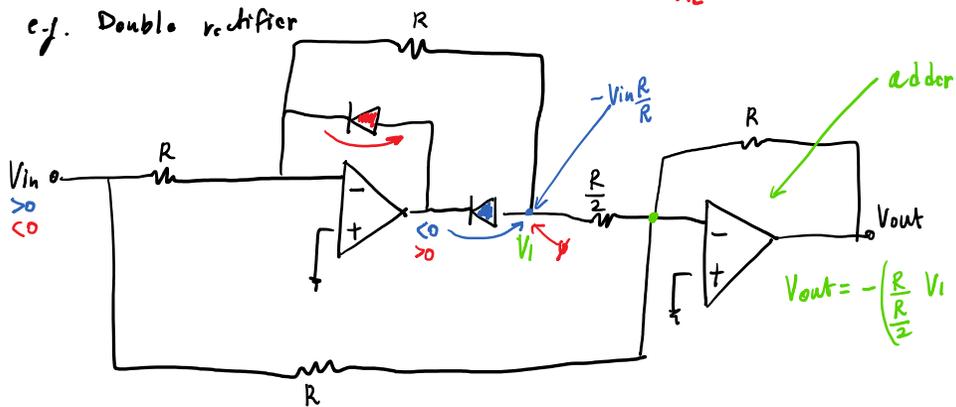
• $V_I < V_r \rightarrow V_{out} = -V_{DD}$

$\hookrightarrow V_{in} = V_{TH} = \frac{R_f + R_i}{R_f} V_r - \frac{R_i}{R_f} (-V_{DD})$

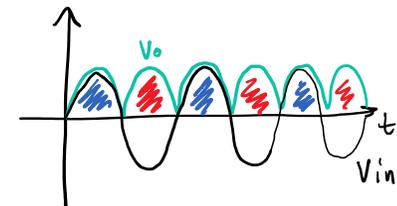
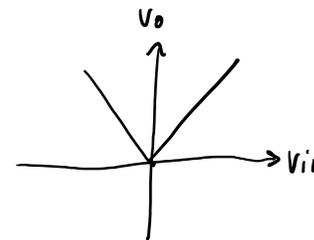


$V_I = V_{in} \frac{R_f}{R_f + R_i} + V_{out} \frac{R_i}{R_f + R_i}$

• e.g. Double rectifier

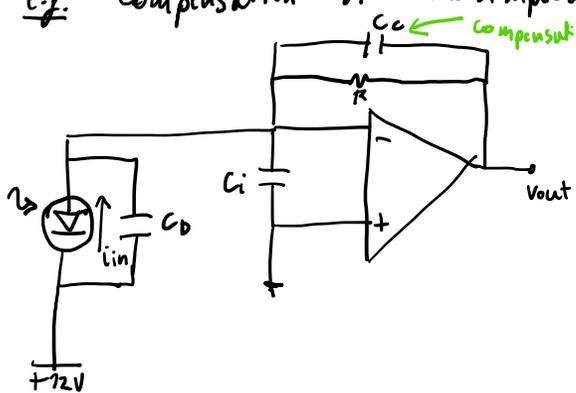


$V_{out} = -\left(\frac{R}{R} V_i + V_{in} \frac{R}{R}\right) = \begin{cases} 2V_{in} - V_{in} = V_{in} > 0, V_{in} > 0 \\ -V_{in} > 0, V_{in} < 0 \end{cases}$

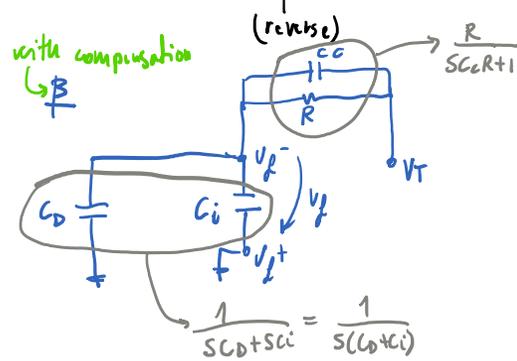


Compensation of particular stages

e.g. Compensation of transimpedance amplifier (photo diode amplifier)



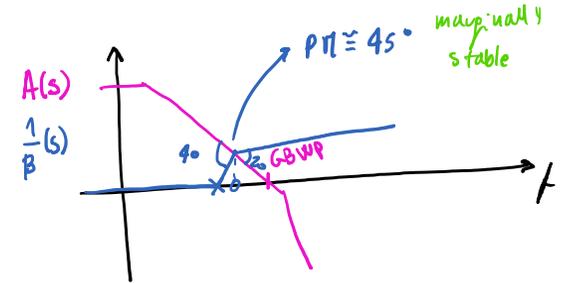
with compensation



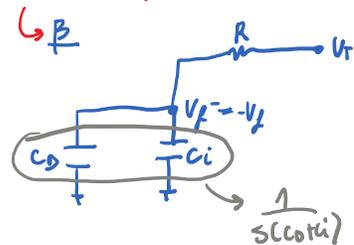
$$V_{p-} = -V_f = \frac{\frac{1}{s(C_D + C_i)} V_T}{\frac{1}{s(C_D + C_i)} + \frac{R}{sC_c R + 1}} = \frac{sC_c R + 1}{s(C_D + C_i)R + sC_c R + 1} V_T = \frac{sC_c R + 1}{s(C_c + C_D + C_i)R + 1} V_T$$

$$\beta_{comp} = - \frac{sC_c R + 1}{s(C_c + C_D + C_i)R + 1}$$

\nearrow zero 0
 \searrow pole x



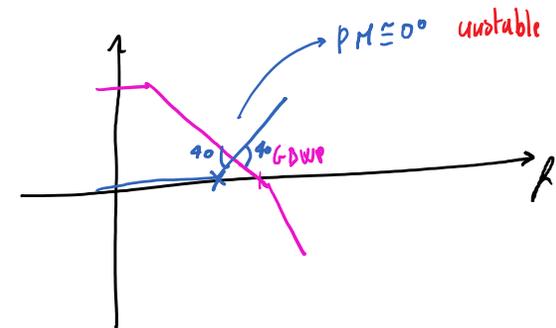
without compensation



$$V_{p-} = -V_f = \frac{\frac{1}{sC_D + C_i} V_T}{\frac{1}{s(C_D + C_i)} + R} = \frac{1}{s(C_D + C_i)R + 1} V_T$$

$$\beta_{uncomp} = - \frac{1}{s(C_D + C_i)R + 1}$$

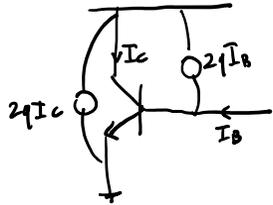
\searrow pole x



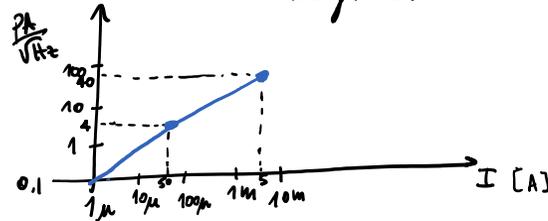
Noise: BJT, diodes

Shot noise: dominant in BJT and diodes

o BJT: shot noise power spectrum: $S(f) \cong 2qI = \frac{\sigma^2}{\Delta f} \rightarrow \sigma^2 = 2qI \Delta f$ \propto white noise



$$2qI_C = 2q\beta I_B$$



DC current through BJT \rightarrow BW of measuring instrument

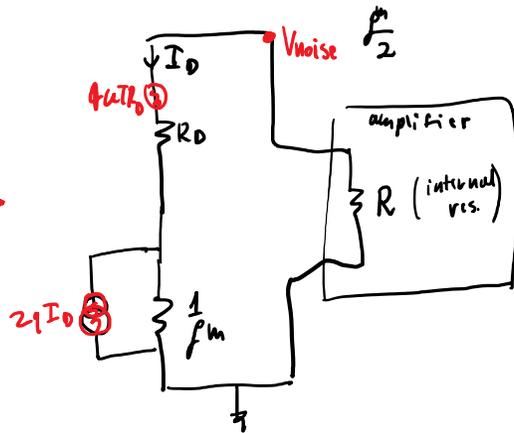
o diodes: dominant shot noise: $2qI_0 \Delta f = \langle i^2 \rangle = \sigma^2 = 4kT \frac{1}{2kT} I_0 \Delta f \rightarrow$ like thermal noise with eq. resistance $R_{eq} = \frac{2}{f_m}$

(also some flicker, but negligible)

$$\sigma_{R_{IT}}^2 = \frac{4kT}{R_{eq}}$$



noise



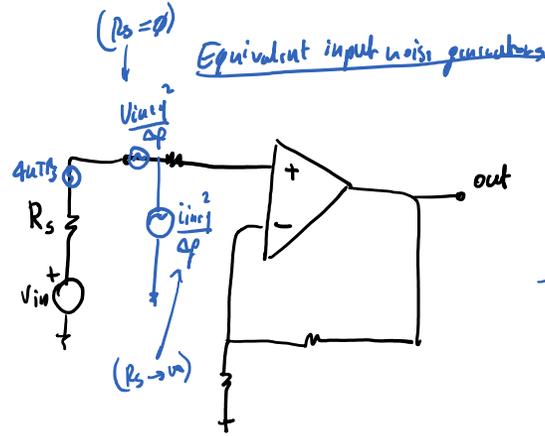
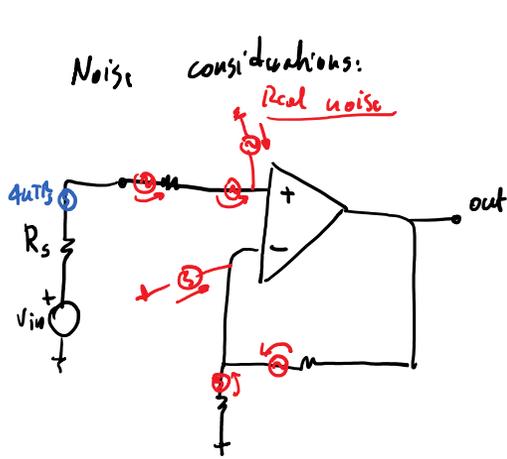
$$\rightarrow \frac{V_{noise}^2}{\Delta f} = 2qI_0 \left(\frac{\frac{1}{f_m}}{\frac{1}{f_m} + R_0 + R} \right)^2 \cdot R^2 + 4kTR_0 \left(\frac{R}{R + \frac{1}{f_m} + R_0} \right)^2$$

$\propto \frac{1}{I_0}$ $\propto I_0, R$

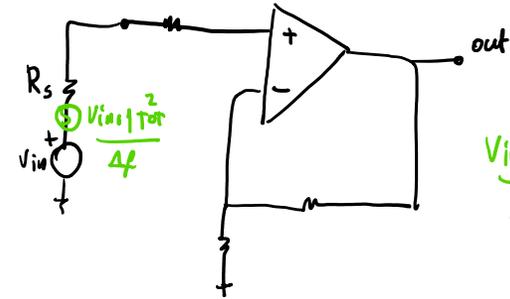
$$\left(\frac{1}{f_m} = \frac{kT}{qI_0} \right)$$

Noise: NF

Noise considerations:



Thermin equivalent generator



$$\frac{V_{inop}^2}{\Delta f} = 4kTR_s + \frac{V_{inop}^2}{\Delta f} + \frac{i_{inop}^2}{\Delta f} R_s^2$$

NF = Noise Figure (F linear scale) $\rightarrow NF = 10 \log_{10} F$
 (NF log scale)

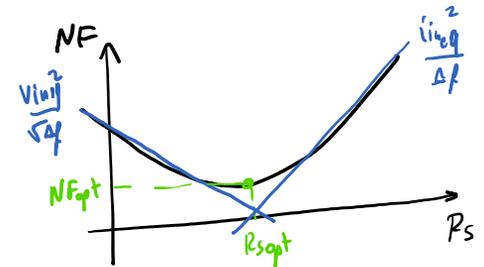
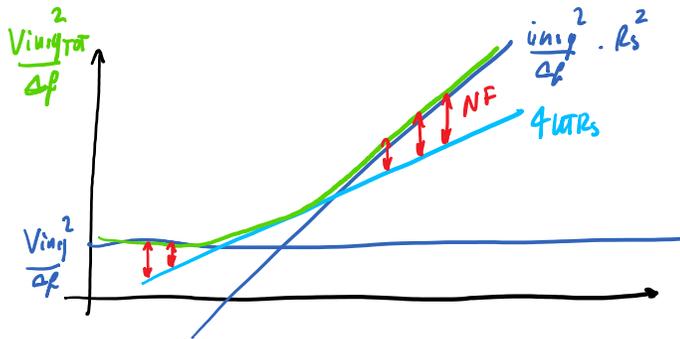
$$F = \frac{SNR_{in}}{SNR_{out}} = \frac{S_{in}}{S_{out}} \frac{N_{out}}{N_{in}} = \frac{N_{out}}{G \cdot N_{in}} = \frac{\text{tot out noise}}{\text{out noise due just to } R_s} = \frac{V_{inop}^2 / \Delta f}{4kTR_s}$$

$$\rightarrow NF = 10 \log_{10} \left(\frac{4kTR_s + \frac{V_{inop}^2}{\Delta f} + \frac{i_{inop}^2}{\Delta f} R_s^2}{4kTR_s} \right) = 10 \log_{10} \left(1 + \frac{V_{inop}^2}{\Delta f} \frac{1}{4kTR_s} + \frac{i_{inop}^2}{\Delta f} \frac{R_s^2}{4kTR_s} \right)$$

Optimum

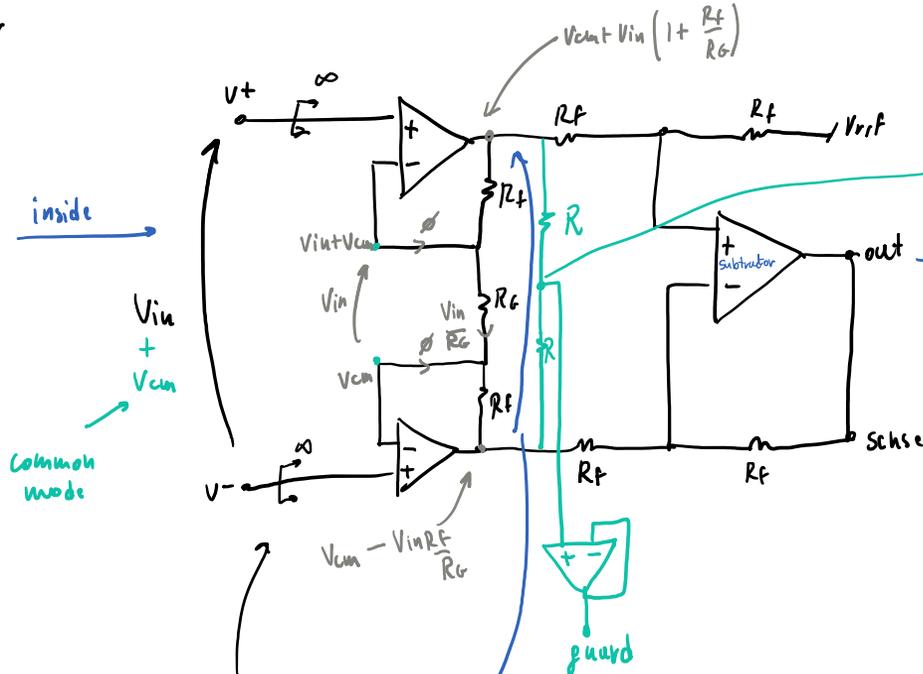
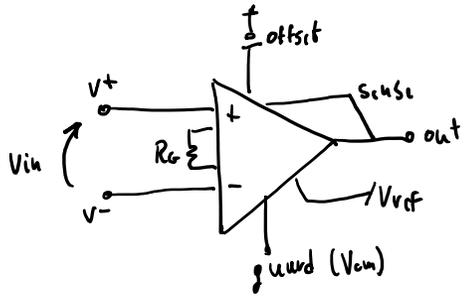
$$\frac{dF}{dR_s} = -\frac{\left(\frac{V_{inop}^2}{\Delta f}\right)^2 \frac{1}{4kT}}{\left(4kTR_s\right)^2} + \frac{i_{inop}^2}{\Delta f} \frac{2R_s}{4kT} = 0$$

$$\rightarrow R_{sopt} = \sqrt{\frac{V_{inop}^2}{\Delta f} \frac{1}{i_{inop}^2 \Delta f}}$$



INA

INA = Instrumentation Amplifier



inside
Common mode
Vin + Vcm

for $V_{in} = 0$

$$V_{guard} = \left[V_{cm} + V_{in} \left(1 + \frac{R_F}{R_G} \right) \right] \cdot \frac{R}{2R} + \left[V_{cm} - V_{in} \frac{R_F}{R_G} \right] \cdot \frac{1}{2} = V_{cm}$$

$$V_{out} = v_{out,diff} + V_{ref} = G_{INA} V_{in} + V_{ref}$$

$$V_{out,diff} = \cancel{V_{cm}} + V_{in} \left(1 + \frac{R_F}{R_G} - \left(-\frac{R_F}{R_G} \right) \right) - \cancel{V_{cm}} = V_{in} \left(1 + 2 \frac{R_F}{R_G} \right) = G_{INA} V_{in}$$

Common mode rejection

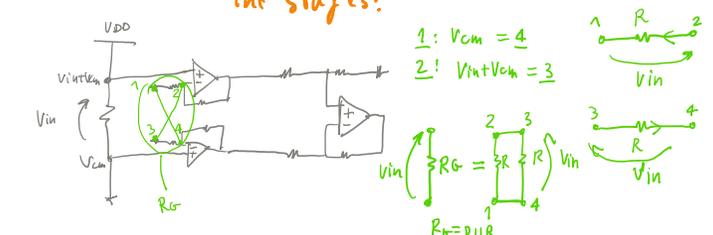
- Pros:
- precise, accurate and reliable gain
 - high input impedance extremely high (Voltage divider)
 - extremely low output impedance
 - extremely high CMRR (Common Mode Rejection Ratio)

Why the use of R_G ?

1st reason: • To read the differential input signal we could use buffer, but it's better to put the buffers at the end and amplify first. → so we don't have noise amplification

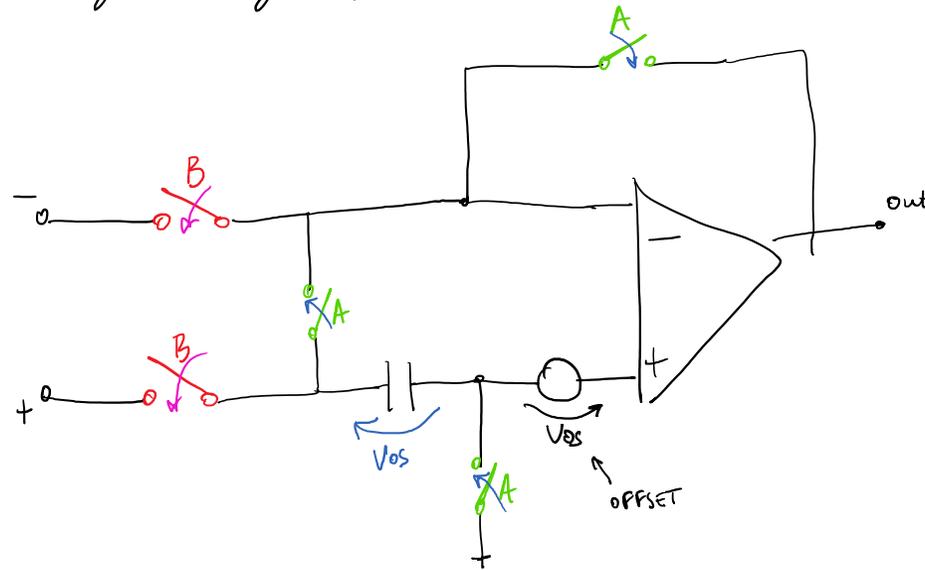
$V_{in} \rightarrow [XG] \rightarrow [X1] \rightarrow \text{out}$

2nd reason: The previous solution if there's V_{cm} it could easily saturate due to the amplification. → So we can connect in this way the stages:



CAZ OpAmp

CAZ = Commutating Auto Zeroing OpAmp



Operation to cancel out the offset V_{os} :

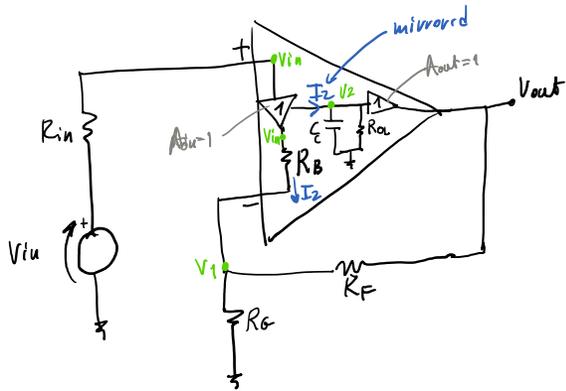
• close A \rightarrow V_{os} on capacitor

• close B \rightarrow V_{os} cancel out

(not used in LNA \rightarrow repeated switching creates disturbances)

CFA

CFA = Current Feedback Amplifier



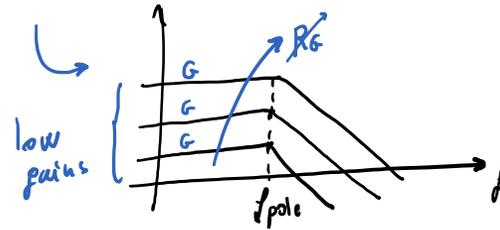
$$I_2 = \frac{V_{in} - V_1}{R_B} = \frac{V_1}{R_G} + \frac{V_1 - V_{out}}{R_F}$$

$$I_2 = \frac{V_2}{R_{ol}} (1 + S C_c R_{ol}) = V_{out} \frac{(1 + S C_c R_{ol})}{R_{ol}}$$

$V_2 = \frac{V_{out}}{A_{out}} \approx V_{out}$
 ← buffer $A_{out} = 1$

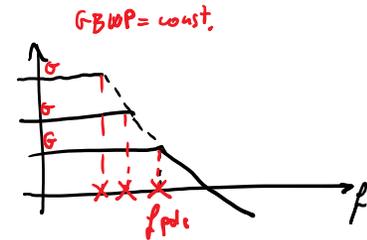
$$f_{pole} = \frac{A_{out}}{2\pi \left[R_F + \left(1 + \frac{R_F}{R_G} \right) R_B \right] C_c}$$

• At LOW GAIN ($G \ll \frac{R_F}{R_G}$) $\rightarrow f_{pole} = \frac{1}{2\pi R_F C_c}$ → doesn't depend on gain (R_F varying)



$\beta \propto R_F$ (not on R_G)

• At HIGH GAIN ($G \gg \frac{R_F}{R_G}$) $\rightarrow f_{pole} = \frac{1}{2\pi G R_B C_c} \rightarrow G \cdot BWP = f_{pole} \cdot G = \frac{1}{2\pi R_B C_c} = \text{const}$



LIKE VOA

$$SR = \left. \frac{dV}{dt} \right|_{\max} = \frac{I_{\max}}{C_c} \approx \frac{V_{step}}{R_F C_c}$$

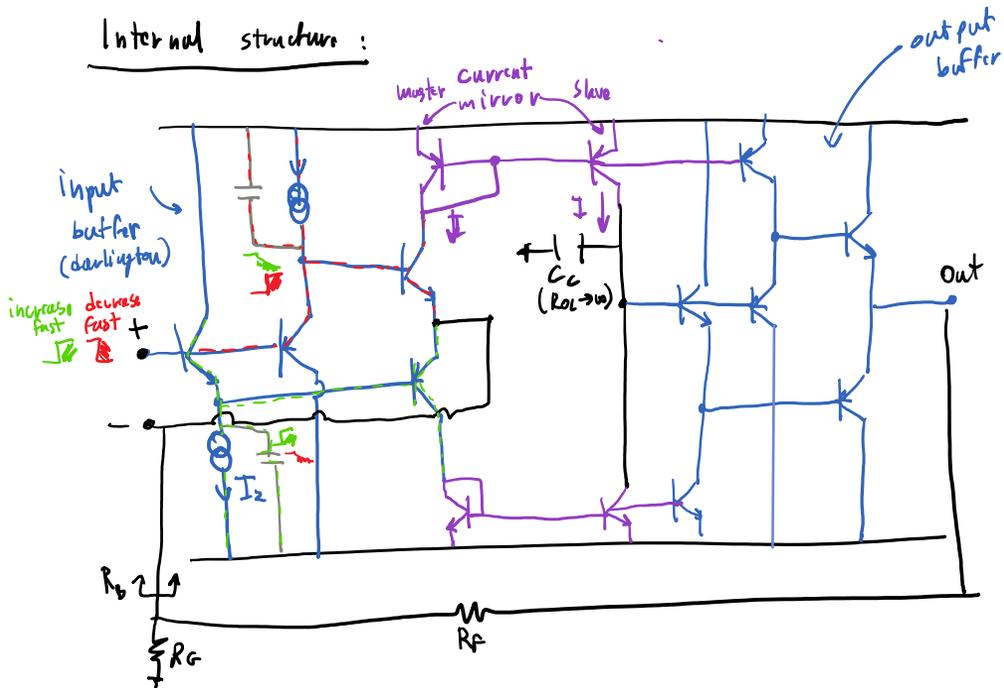
Notes: • To speed up the circuit we can use double emitter BJTs

• To reduce offset add transistors (e.g. diodes)

Pro: • $G \cdot BWP \neq \text{const.}$ (for low gain)
 • improve offset and SR

Cons: • errors that can be comp. via proper circuits:
 • temp. offsets
 • SR due to slow dyn.
 • current mirrors can be improved
 • cross-cross can be used

Internal structure:

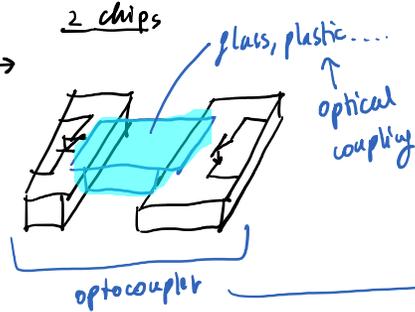


ISO

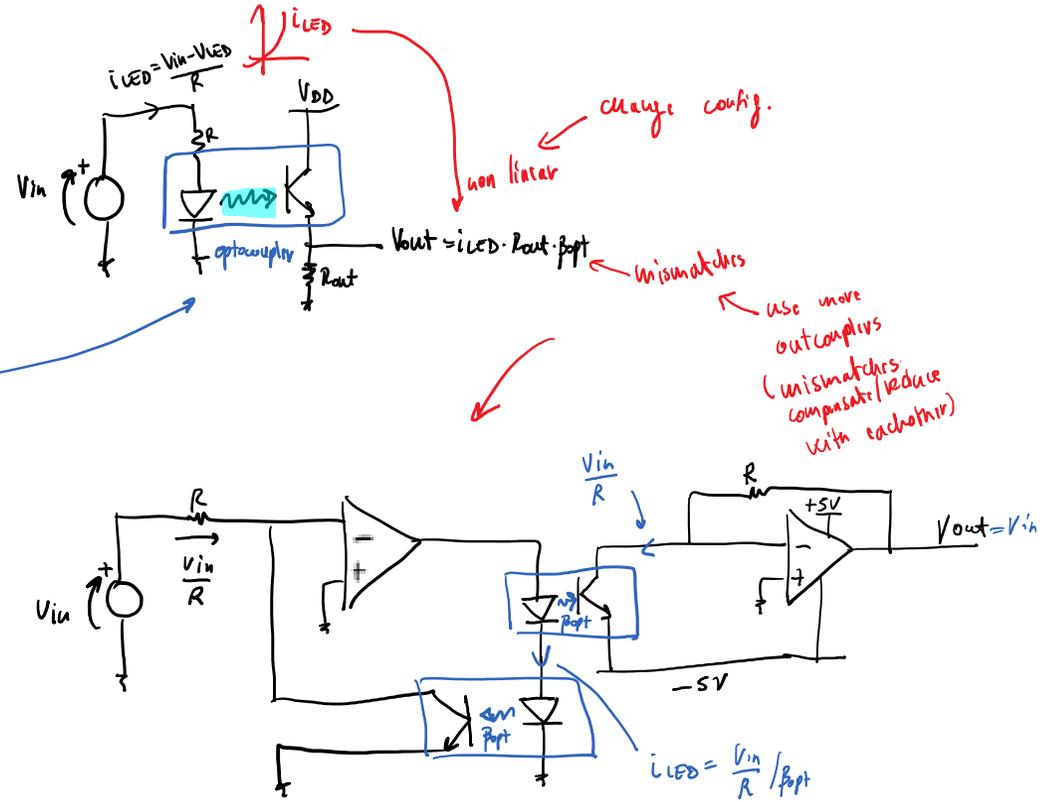
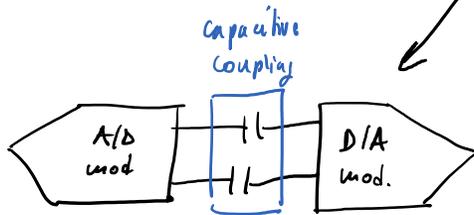
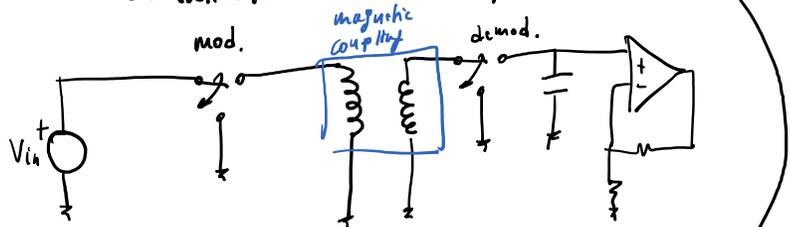
ISO = Isolation Amplifier

Type of isolation:

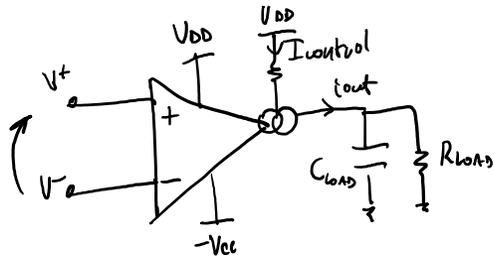
- optical → most common
- magnetic
- capacitive



modulation/demodulation techniques



OTA



- Pro:
- all low-impedance nodes
 - wide BW $\rightarrow f_p = \frac{1}{2\pi C_{load} R_{load}}$

- Cons:
- no infinite gain
 - no virtual ground
 - it is used open-loop
 - strong non-linearity

Translinear principle
 $I_D^+ I_C^+ = I_D^- I_C^-$

$$\begin{cases} I_D^+ = I_D - I_{in} \\ I_D^- = I_D + I_{in} \end{cases}$$

$$(I_D - I_{in}) I_C^+ = (I_D + I_{in}) I_C^-$$

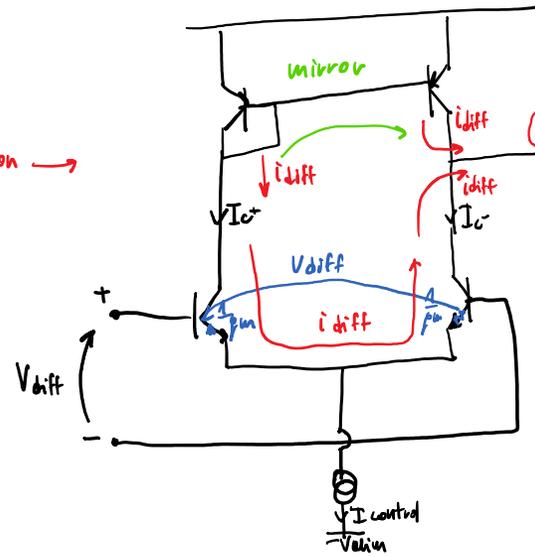
$$I_D (I_C^+ - I_C^-) = I_{in} (I_C^+ + I_C^-)$$

$$I_D \frac{i_{out}}{I_{control}} = I_{in} \frac{I_{control}}{I_D}$$

$$i_{out} = \frac{I_{control}}{I_D} I_{in}$$

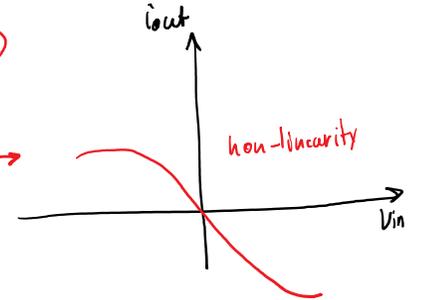
Internal Architecture

Without linearization \rightarrow

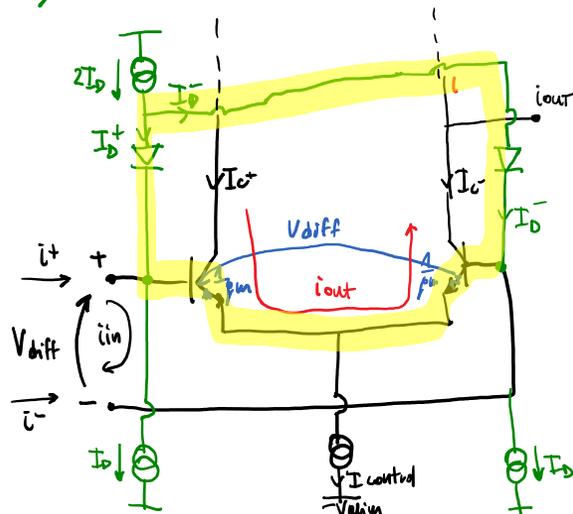


$$i_{out} = 2i_{diff} = \frac{2}{\beta \cdot \frac{1}{\mu_n}} V_{diff} = G_m V_{diff}$$

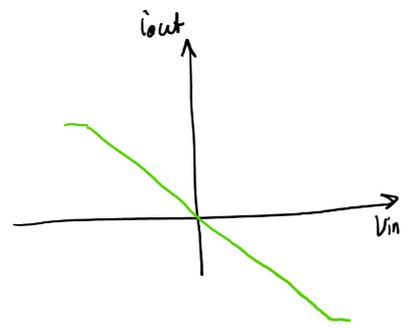
$$G_m = \frac{I_{control}}{2 \cdot 25mV}$$



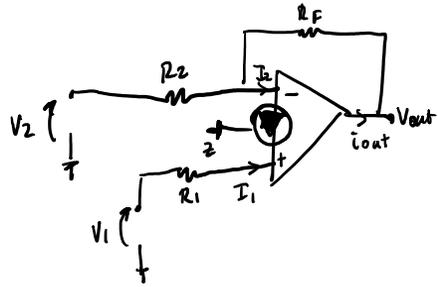
with linearization diodes \rightarrow



linearization \rightarrow



NORTON



$$I_1 = \frac{V_1}{R_1} \quad I_2 = \frac{V_2}{R_2} + I_{out}$$

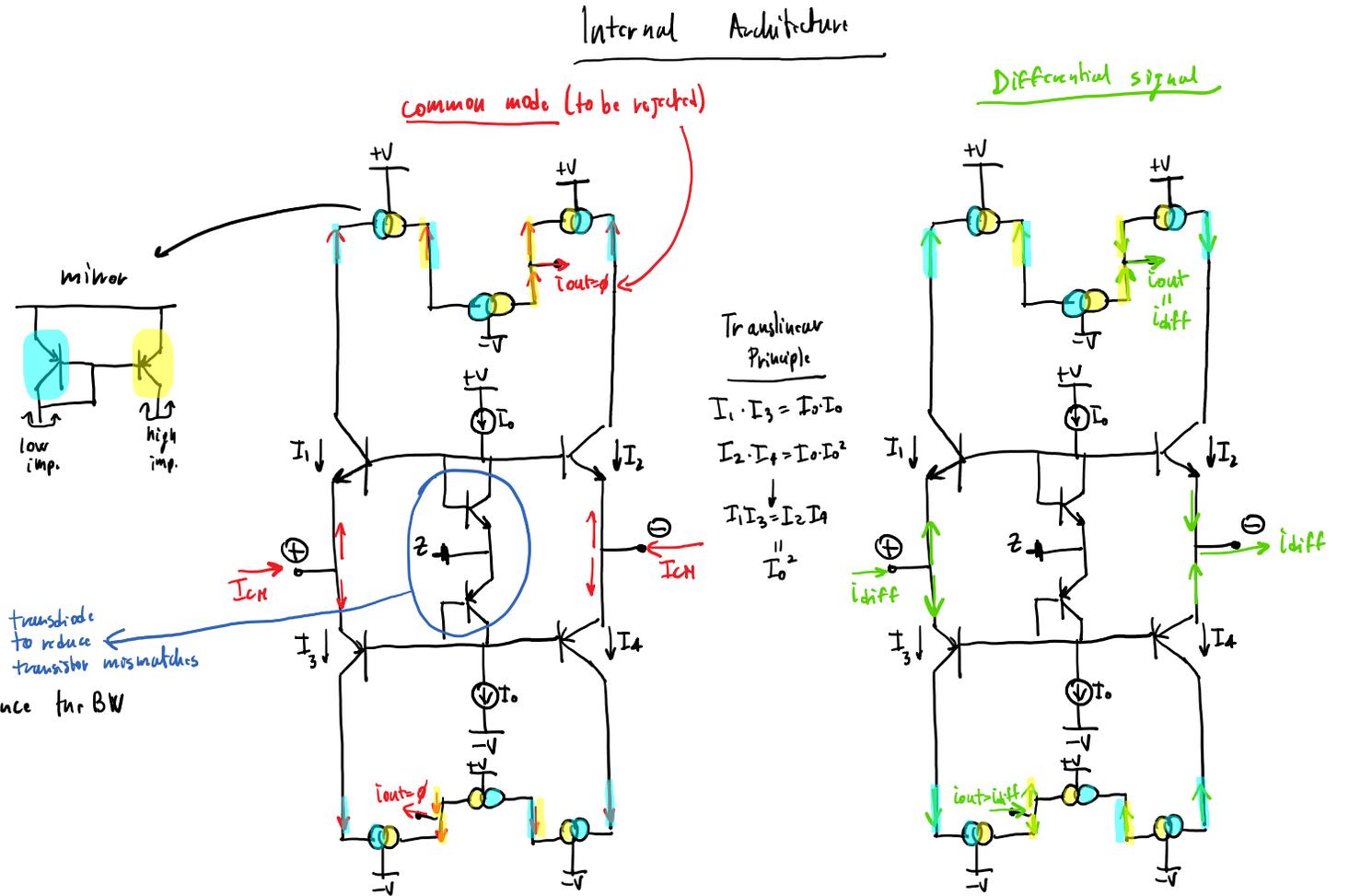
$$I_{out} = \frac{V_{out}}{R_F} \quad I_{out} = A_i (I_1 - I_2) \Rightarrow A_i \left(\frac{V_1}{R_1} - \frac{V_2}{R_2} - I_{out} \right)$$

$$\Rightarrow I_{out} = \frac{A_i}{1 + A_i} \left(\frac{V_1}{R_1} - \frac{V_2}{R_2} \right)$$

$$V_{out} = \frac{A_i}{1 + A_i} \left(V_1 \frac{R_F}{R_1} - V_2 \frac{R_F}{R_2} \right)$$

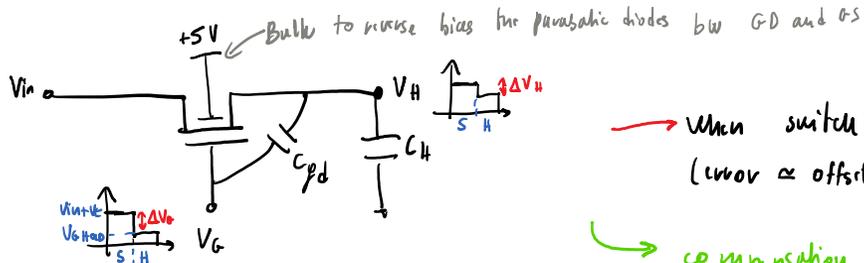
- Pro:**
- It is able to read current inputs
 - all nodes have low impedance \rightarrow parasitic C don't influence the BW
 - very high BW (independent from closed-loop gain)

- Cons:**
- Finite and usually small $A_i \rightarrow$ No ideal gain behaviour
 - Gain depends on external load



S/H: errors

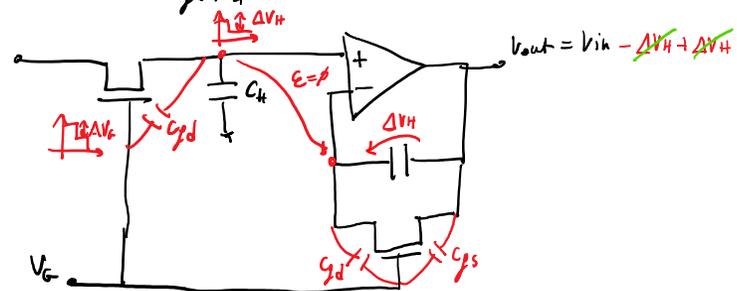
Charge injection



→ When switch open we have a charge injection due to parasitic capacitance C_{pD} (error \propto offset)

$$\Delta V_H = \Delta V_a \frac{C_{pD}}{C_d + C_H}$$

→ compensation:

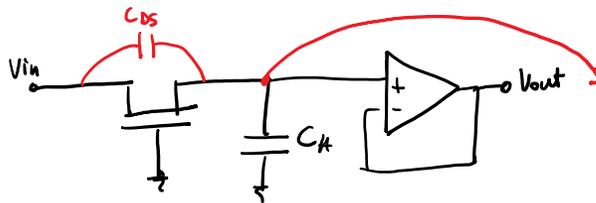


Aperture induce non-lin.

→ Actually charge injection is not const. (not offset but non-lin.)

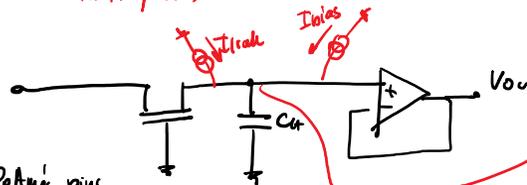
↳ it depends on $V_{in} \Rightarrow \Delta V_{G1max} = V_{in,max} + V_t - V_{G,hold}$

Signal feedthrough

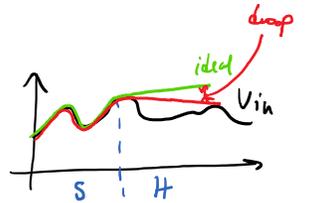


(perturbation in H phase)

Drop: CH discharge during H phase due to I_{leak}(MOS) and I_{bias}(OpAmp)



$$\Delta V_H = \frac{I_{leak} + I_{bias}}{C_H} t_{drop}$$

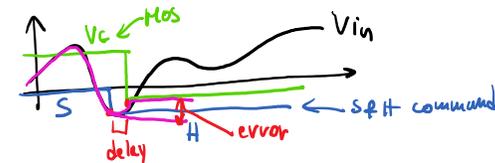


Buffer induced non-lin.: Due to residual voltage difference E b/w the two OpAmp's pins

make sure $A_o > \frac{V_{out,max}}{E}$

Aperture-delay time: Due to propagation of the control command

↳ the actual opening of the switch (MOS) will have a delay w.r.t S/H command

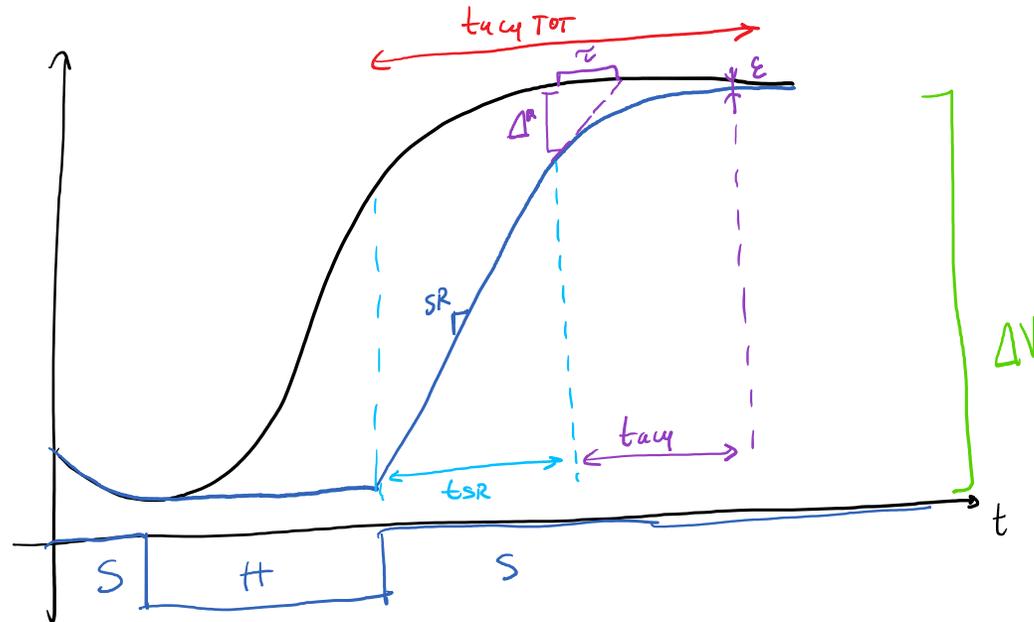


Aperture time jitter: Actually aperture delay is not deterministic because of noise → fluctuations



$$\sigma_{tjitter} = \frac{\sigma_{th}}{V_{command} / t_{command}}$$

S/H: Acquisition time



$$t_{acqTOT} = t_{SR} + t_{acq}$$

$$\uparrow SR \left\{ \begin{array}{l} SR = \frac{dV_{out}}{dt} \\ \frac{dV_{out}}{dt}_{max} = \frac{I_{outmax}}{C} \end{array} \right\} \rightarrow \text{choose max}$$

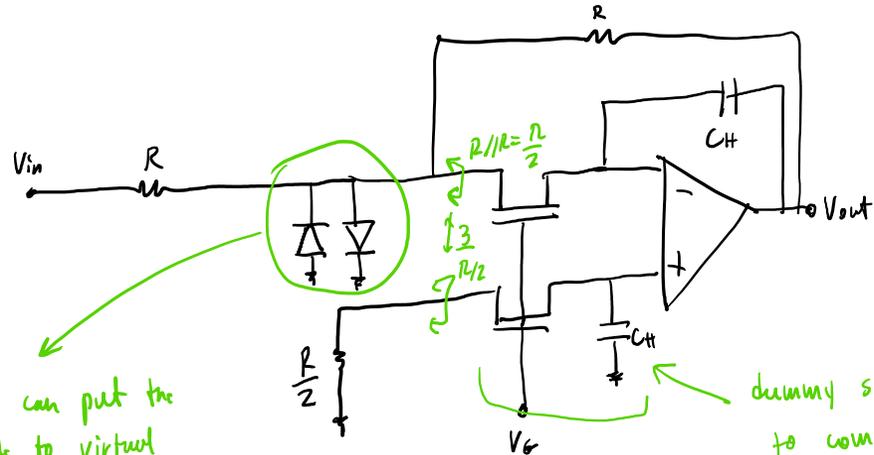
$$\hookrightarrow t_{SR} = \frac{\Delta V - \Delta^+}{SR}$$

$$\uparrow SR = \frac{\Delta^+}{\tau} \rightarrow \tau = \frac{\Delta^+}{SR}$$

Exponential charge

$$t_{acq} = \tau \ln \frac{\Delta^+}{\epsilon}$$

S/H: simple driving

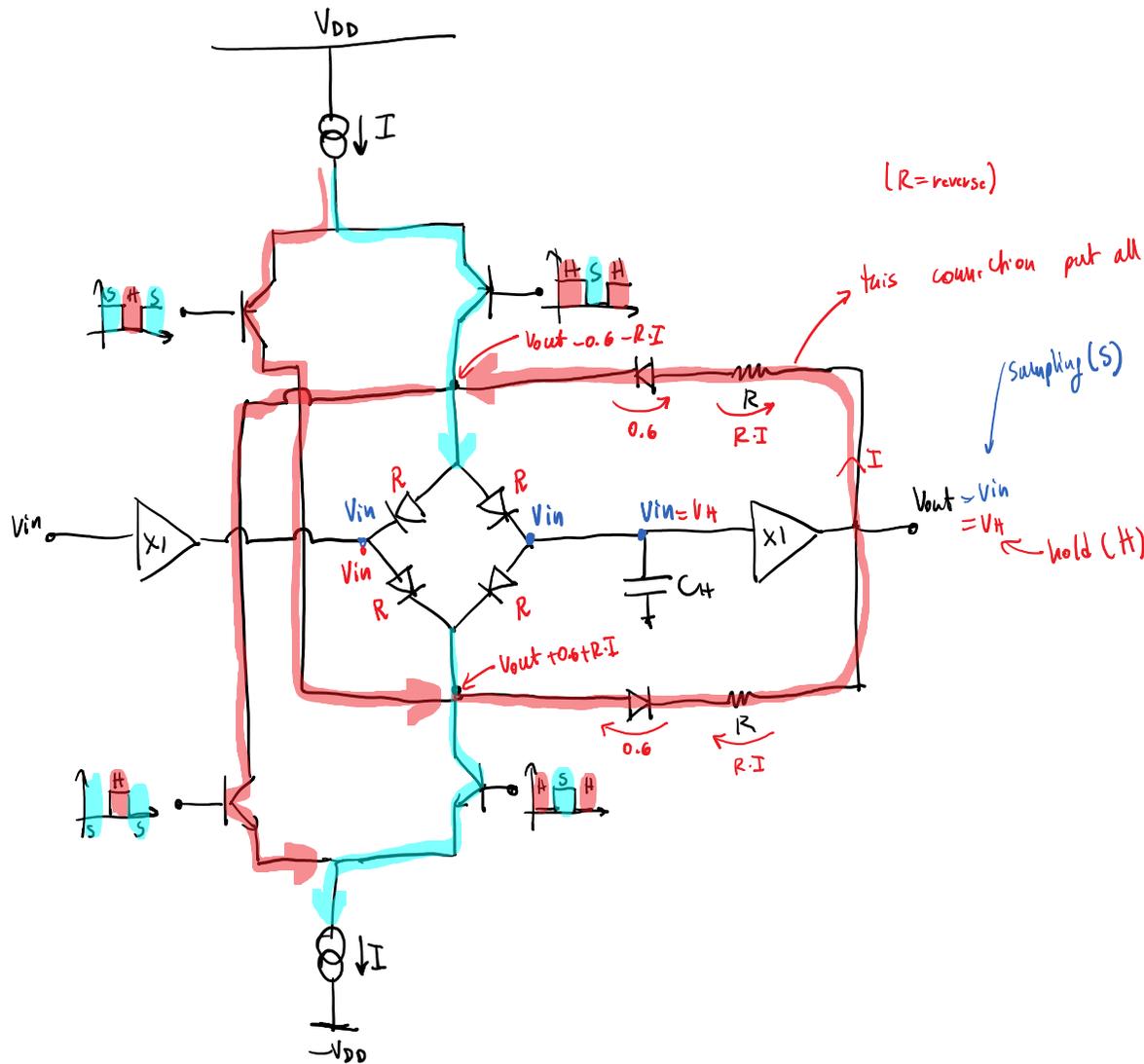


We can put the node to virtual ground when MOS on and that voltage is always $\in [-0.6 \div 0.6V]$
 $\rightarrow \Delta V_G$ excursion is small and const $\rightarrow 1$

dummy structure to compensate charge injection $\rightarrow 2$

- Pro:
1. V_G simple CMOS levels ($0 \div 3.3V$), indep. from V_{in}
 2. reduction of Aperture induced non-lin.
 3. compensates bias currents effects

S/H: fast switching



(R = reverse)

otherwise it would have been a non-volatile capacitor
 this connection put all the diodes of the bridge in reverse during H phase



Pros:

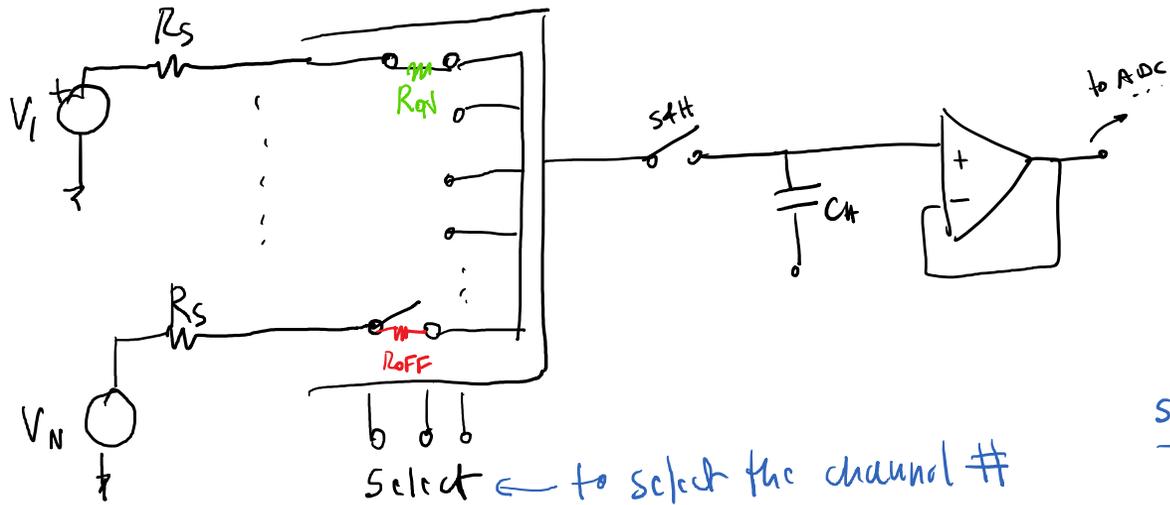
- very fast switch with diodes

Cons:

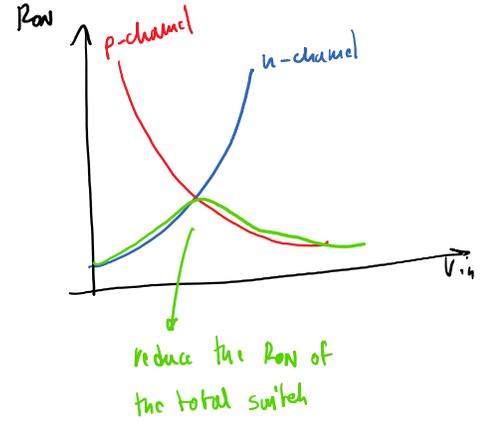
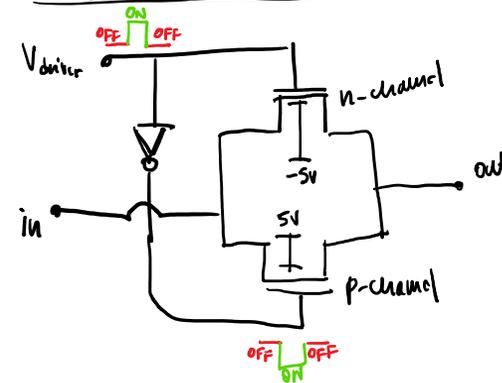
- mismatches b/w components → error on V_H
- Synchronization is needed b/w bipolar S/H command signals

MUX

Multiplexer = acquire analog signals from various sources (channels) and process them by means of a single digital process



Analog switch for MUX: Pass-transistor



Sampling time: $t_{acq/min} = \tau_{max} \ln \frac{\Delta_{max}}{\epsilon_{max}}$

$\tau_{max} = [(N|s|_{max} + R_{ON}|_{max}) \parallel \frac{R_{OFF} + R_S}{N-1}] C (1 + t_{hold,max})$

Hold time: max bw $\left\{ \begin{array}{l} I_{OFF} = (N+1)I_{leak} + I_{bias} \\ I_{OFF} = \frac{V_{in,max}}{R_{OFF,min} + R_{S,min}} \end{array} \right\} \rightarrow t_{HOLD} = \frac{Q \epsilon_{in}}{\frac{I_{OFF}}{C|_{min}}}$

Sampling freq. $T_s = t_{acq/min} + t_{HOLD}$ $f_{s,max} = \frac{1}{T_s} \leftarrow \text{(throughput)}$

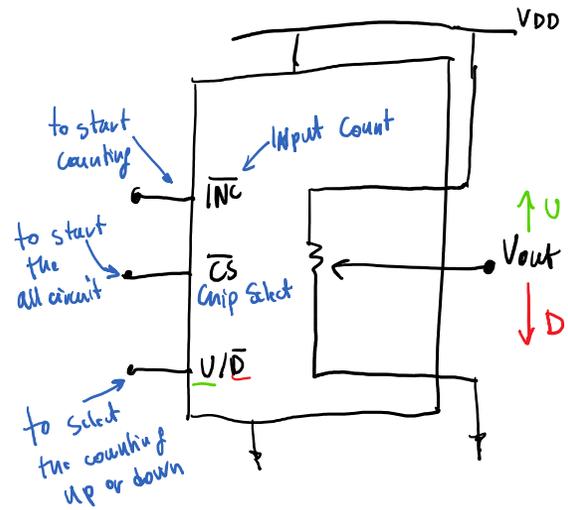
$f_{channel} = \frac{f_{s,max}}{N} \rightarrow \text{Shannon}$ $f_{in,max} = \frac{f_{channel,max}}{2}$ (for each channel)

Scanning for channel with wider BW:

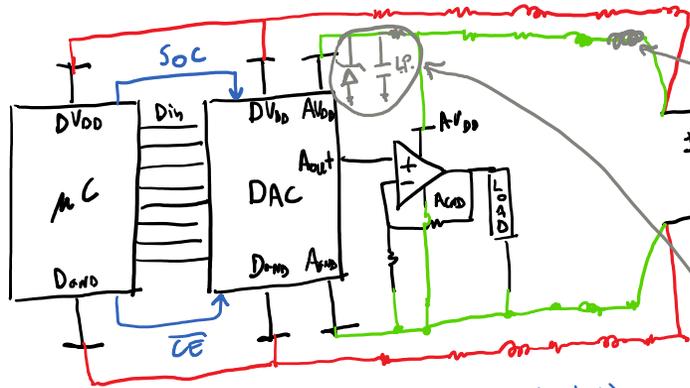
$N = \# \text{ channels}$
 $K = \# \text{ priority wide BW channels}$
 $\rightarrow f_{s,K} = \frac{f_{s,max}}{K+1}$ $f_{s,N-K} = \frac{f_{s,max}}{(N+1)(N-K)}$

DigPot

Dig Pot = Digital Potentiometer



DAC



→ To avoid that the digital and analog part induce disturbances bw each other it's better to separate the P.S.

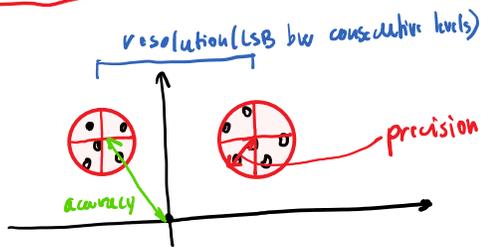
put a low value inductance the big inductances of the P.S.



to avoid high freq. fluctuations caused by

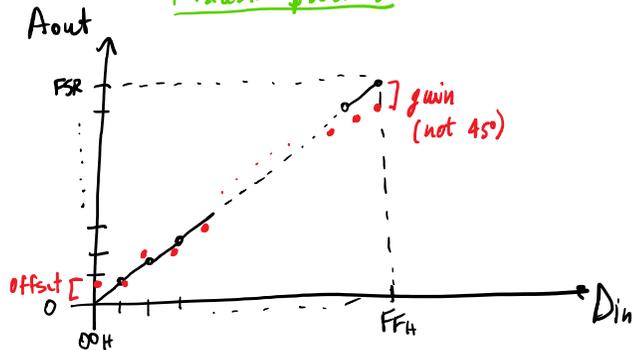
- can put a diode to fix the voltage in case of variable battery (Also on digital part and Vref)
- can put a L.P. filter to filter out any dist.

Performance

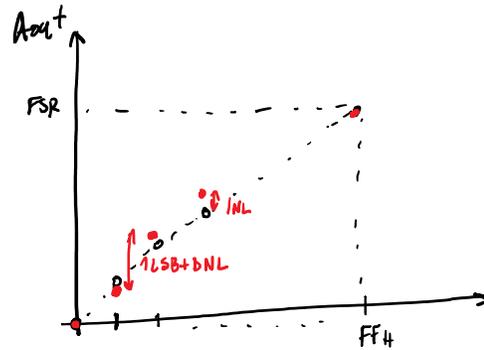


Errors

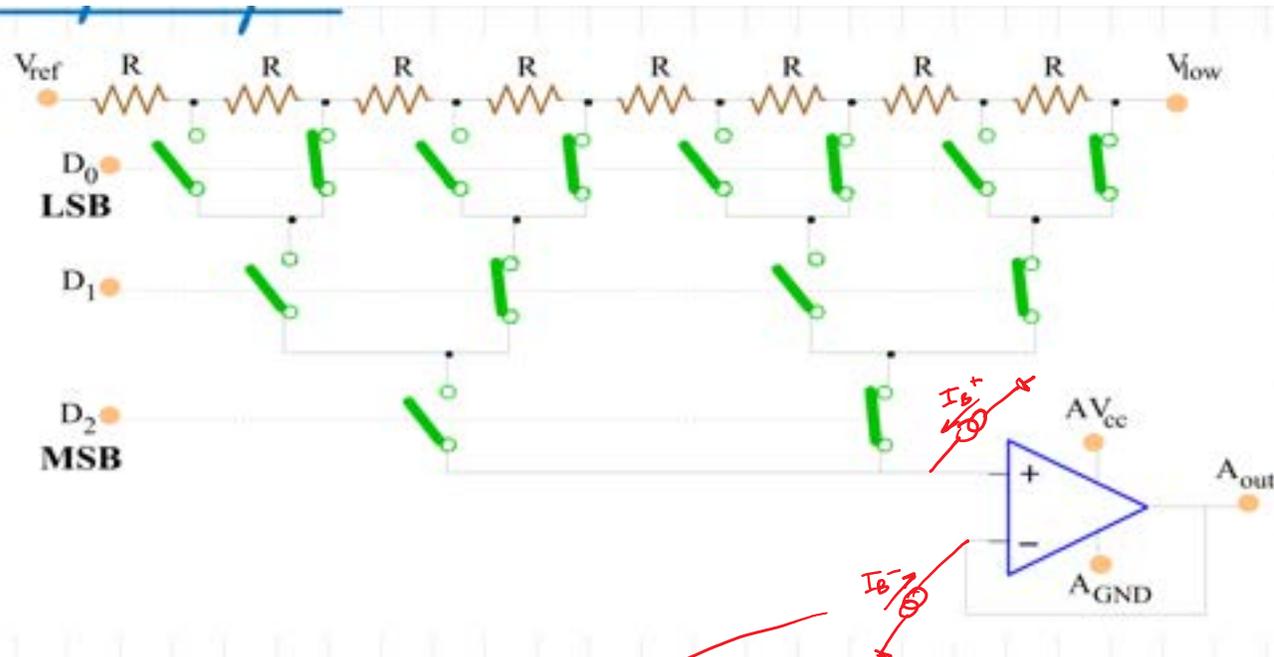
Fixable problems



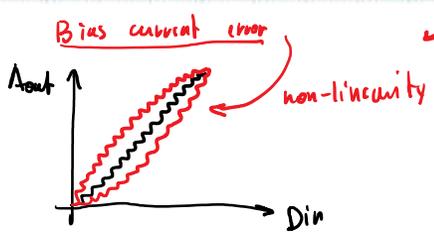
Non-linear errors



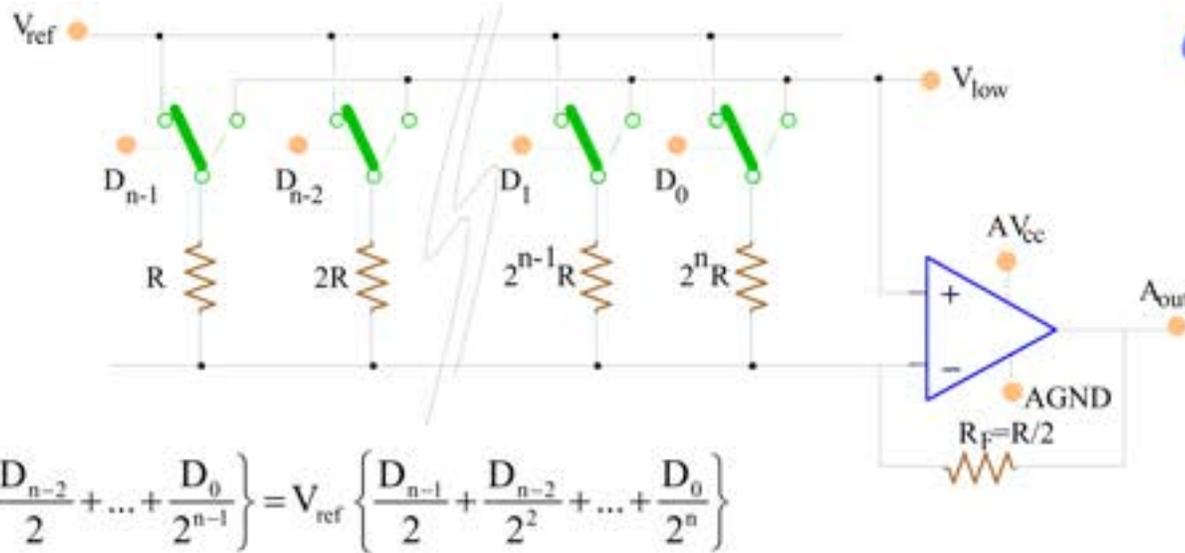
DAC: Voltage scaling DAC



- Components:**
- 2^N Resistors \rightarrow divide F_{SP} in 2^N voltage level
 - 2^{N+2} MOS \rightarrow allow to properly select the levels
 - OpAmp
- Pros:**
- easy scalability of all resistors
 - MOS switching efficient and less expensive than A. MUX
- Cons:**
- large # resistors and transistors \rightarrow too much space
 - I_B and I_{leak} cause non-lin.
 - \downarrow OA
 - \downarrow MOS



DAC: Weighted-R DAC



Components: • $>n$ resistors \rightarrow voltage levels

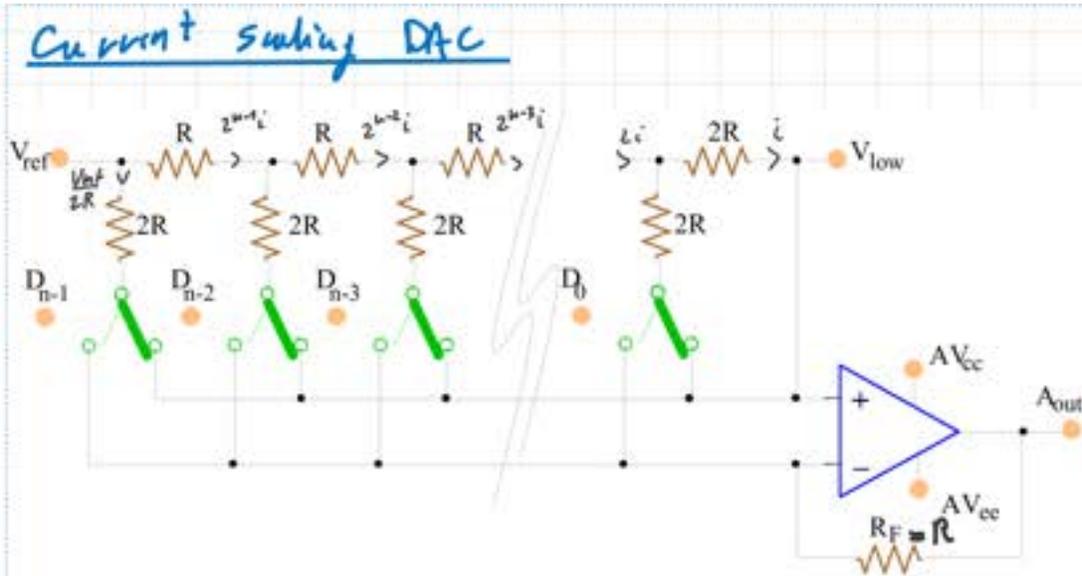
- 2n p/n-MOS
- OpAmp

Pros: • simplest converter

Cons: • different R values + tolerances

- voltage drop on R_{on} , R_s
- variable current consumption
- large silicon area
- I bias errors

DAC: Current scaling (Ladder R-2R) DAC



Components: • $3n$ resistors \rightarrow current divider

• $2n$ MOS \rightarrow switches low levels

• OpAmp

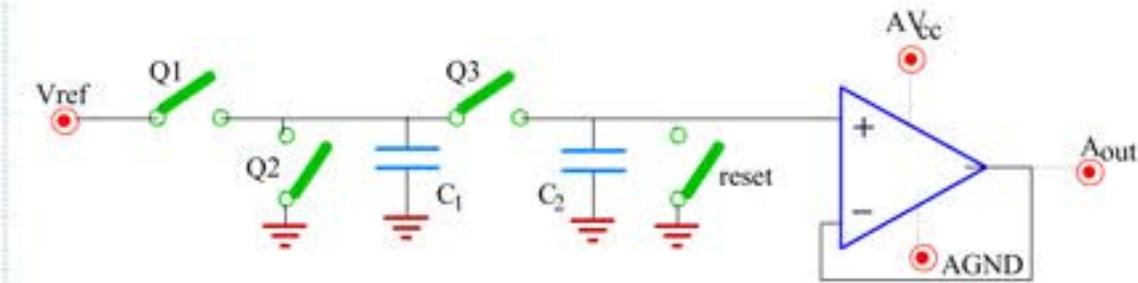
Pros: • easy scalability of resistors

• easy drive of MOS switches \rightarrow RON creates a const. offset (can be compensated)

Cons: • bias currents errors

DAC: Serial input DAC

Serial Input DAC



Components:

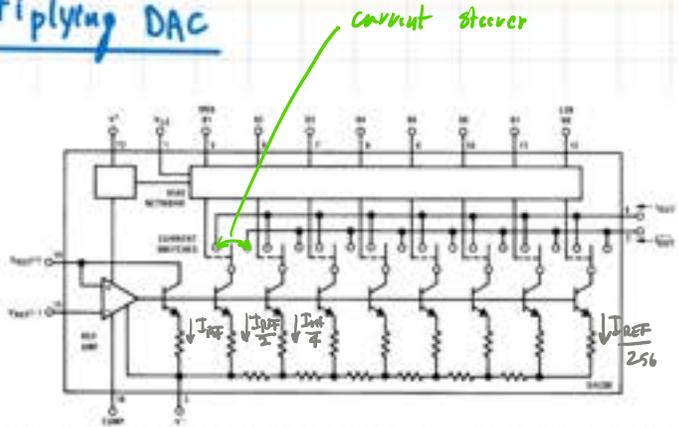
- only 2 capacitors → For store and sharing the bit values $C1$ $C2$
- S MOS → close/open to activate store/share logics

Pros: • Extremely compact and easy

Cons: • individual bits are provided sequentially (Serially) → SLOW

DAC: Multiplying DAC

Multiplying DAC



Pin numbers represent the PDIP package. The SOIC package pin numbers differ from that of the PDIP package.

Components: $\sim 2n$ resistors to provide \bar{I}_{out}, I_{out}

$\sim n$ mirrors + n switches (current steerer)

OpAmp \rightarrow to vary V_{ref}

$$I_{out} = \frac{V_{ref}}{R_{ref}} \cdot \frac{D_{in}}{2^n}$$

variable variable
MULTIPLYING

$$I_{out} + \bar{I}_{out} = I_{FS} = \frac{V_{ref}}{R_{ref}} \frac{255}{256}$$

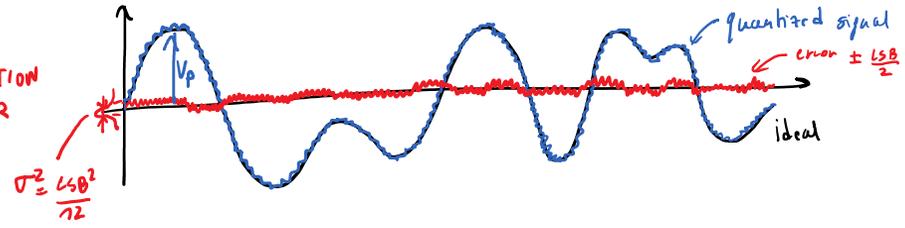
Full Scale

Pros: • We can vary V_{ref} in addition to D_{in}

DAC: Noise analysis

• Din is quantized \rightarrow Aout will be quantized

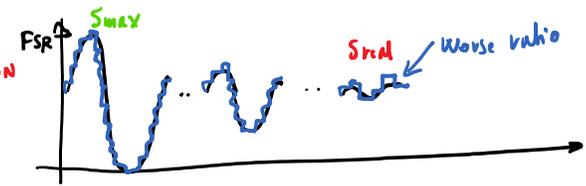
QUANTIZATION ERROR



$$\rightarrow SNR_{id} = \left. \frac{\left(\frac{V_p}{2}\right)^2}{\frac{LSB^2}{12}} \right|_{dB}$$

• Aout can also have had amplification \rightarrow worse ratio w/ quantization

AMPLIFICATION FACTOR

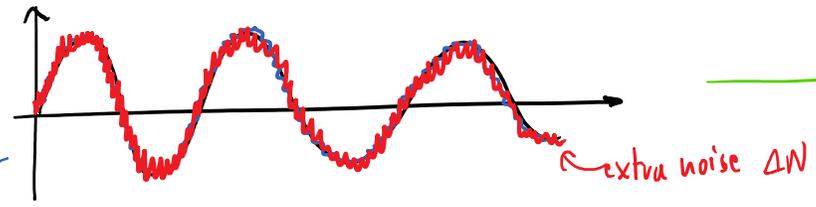


$$\rightarrow SNR_{th} = SNR_{id} - \Delta S \Big|_{dB}$$

$$\Delta S = \frac{S_{max}}{S_{red}}$$

• There can also be extra noise

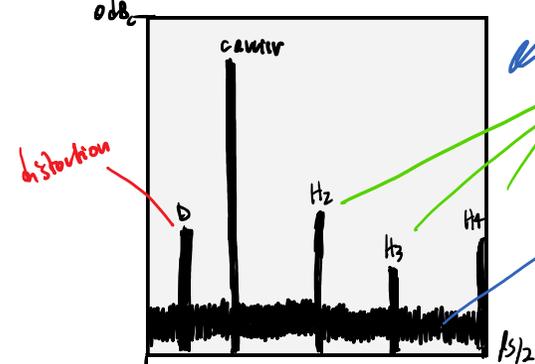
EXTRA NOISE



$$\rightarrow SNR_{real} = \frac{S_{red}}{N_{real}} = \frac{S_{id} \cdot \Delta S}{N_{quant} + \Delta N} = SNR_{id} - \Delta S - \Delta N \Big|_{dB}$$

Spectral performance

- $S_{max} = 0dBc$ ← carrier
- consider just $\frac{f_s}{2}$ and $\frac{N_{samples}}{2}$



after FFT

Harmonics

$$\text{noise floor} = \frac{\text{noise}}{\frac{N_{samples}}{2}} \Big|_{dBc}$$

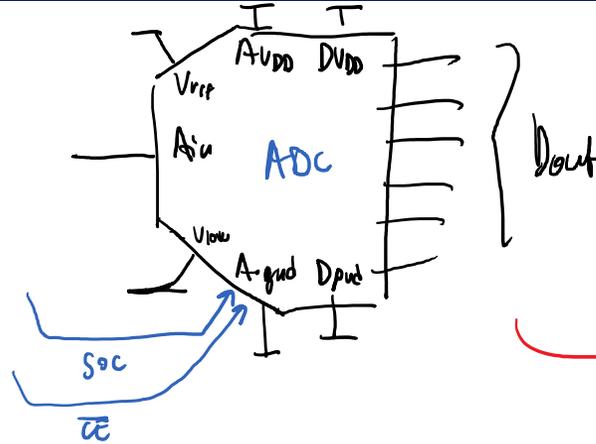
• Total Harmonic Distortion: $THD = \frac{\text{power of all the harmonics}}{\text{power of useful signal}} \Big|_{dB} = \frac{\sum H_i}{S_{red}}$

• Signal to Noise And Distortion: $SINAD = \frac{\text{power of useful signal}}{\text{tot. power of noise and harmonics}} \Big|_{dB} = \frac{S_{red}}{N_{real} + D + \Sigma H_i}$

eq. bit:
 $\rightarrow ENOB = \frac{SNR_{real} - 1.76}{6.02}$

ADC

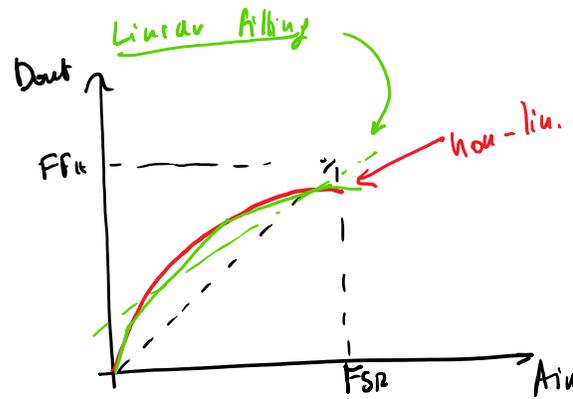
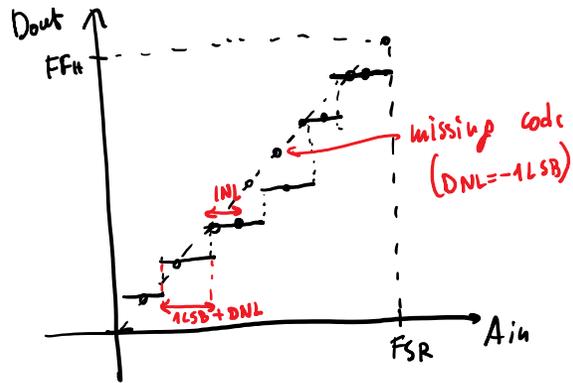
Analog to Digital Converter = ADC



Errors

(offset if min)

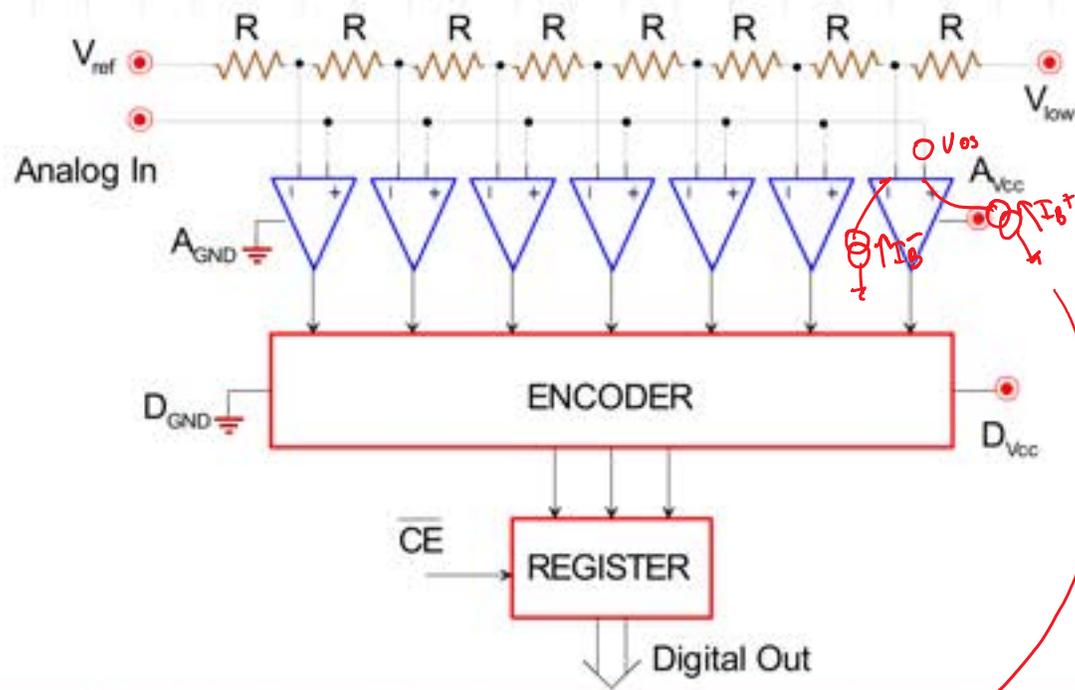
↳ Non-linear errors



→ compromise bw cost. of amplification stages and higher resolution ADCs to convert a small analog signal (proper conditioning based on signal, costs and requirements)

ADC: Flash ADC

Flash ADC



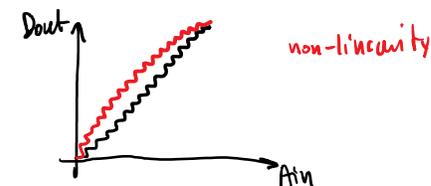
- Components:
- 2^n resistors \rightarrow to create 2^{n-1} quantization levels
 - 2^n comparators \rightarrow compares the q. levels with the input \rightarrow H/L
 - 1 encoder (thermometric code \rightarrow binary code)
 - \rightarrow H/L \rightarrow 0/1

- Pros:
- Very fast \rightarrow parallel conversion
 - simplicity

- Cons:
- silicon area \uparrow and power dissipation \uparrow with $n \uparrow$
 - bias and leakage currents, parasitic capacitors
 - \rightarrow lead to non-lin. of the ADC converter
 - offset lead to incorrect switching
 - \rightarrow missing codes, non-monotonicity of ADC

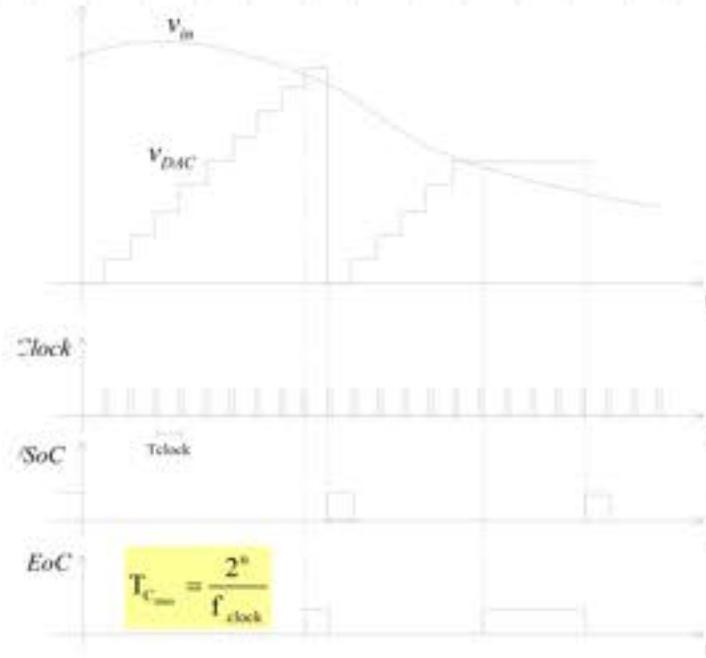
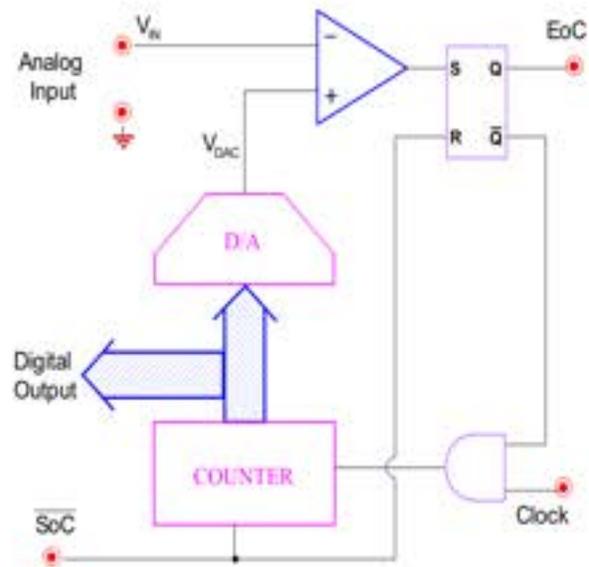
offset errors \rightarrow for low value of LSB, offset can be comparable to a level and result in missing codes

bias current errors \rightarrow can change the comparator switching level and result in non-linearities



ADC: Staircase ADC

Staircase ADC



Components:

- 1 Counter → subsequent adjustments via binary count
- 1 DAC → binary count → analog level to compare with V_{in}
- 1 Comparator

Pros: • precision depends on the DAC

Cons: • Conversion time depend on V_{in}

↳ not very fast

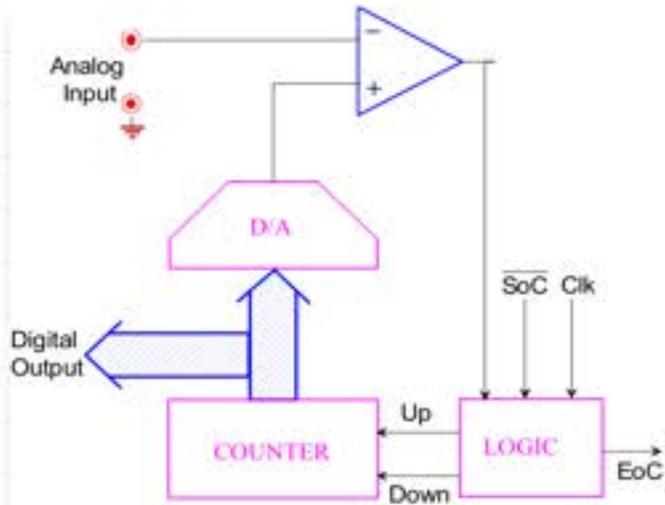
↳ Sampling comb not const.

(not regular sampl. steps due to time dep. on V_{in})

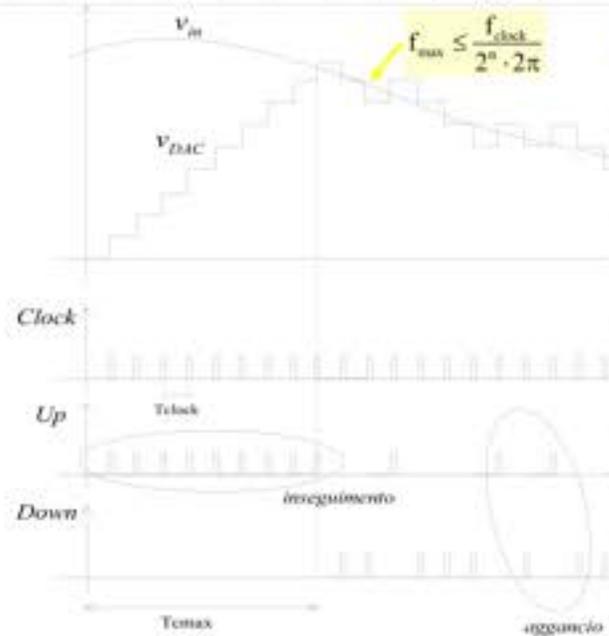
Converts in hold phase ← you can put a S/H before the ADC
↳ regular

ADC: Tracking ADC

Tracking ADC



Components: 1 DAC, 1 counter, 1 comparator, 1 up/down logic



$$f_{max} \leq \frac{f_{clock}}{2^n \cdot 2\pi}$$

Components:

- 1 Counter → subsequent adjustments via binary count
- 1 DAC → binary count \xrightarrow{DAC} analog level to compare with V_{in}
- 1 comparator
- 1 up/down logic → to make the counter go up/down and "track" V_{in}

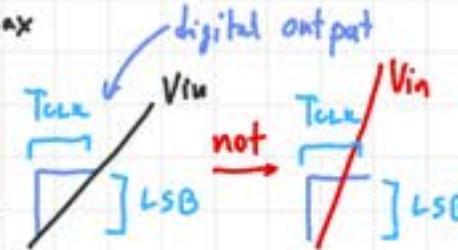
Pros:

- Fast → correct sample at every CLK
- precision depends on DAC
- Oversampling → use just one bit = Up/Down to stay hooked on input signal

(also called Δ modulator)

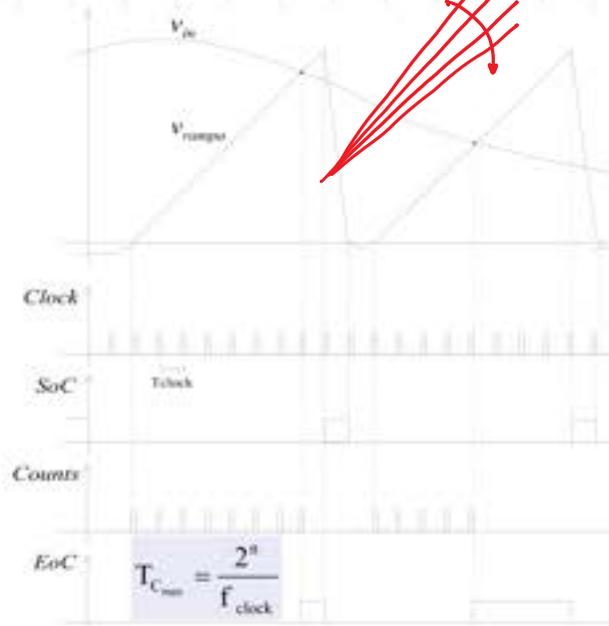
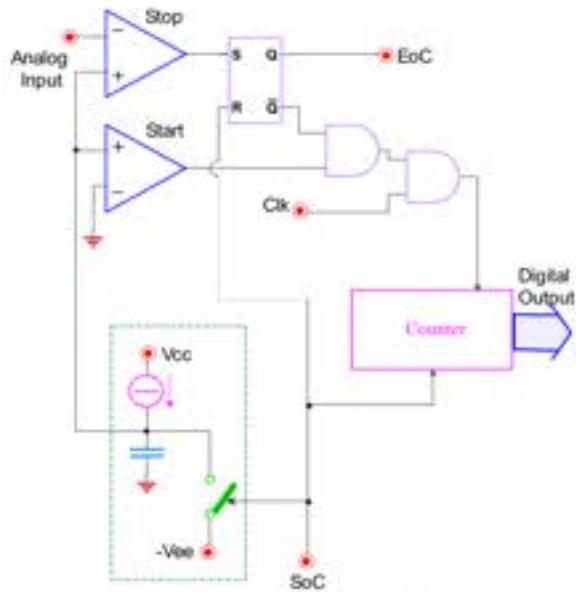
Cons:

- frequency of signal $\gg f_{max}$
- $f_{clk} \geq 2^n \pi f_{max}$
- for high slopes $\left. \frac{dV_{in}}{dt} \right|_{max} < \frac{LSB}{T_{clk}}$



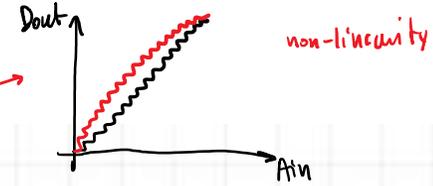
ADC: Single slope ADC

Single-slope ADC



better to use double ramp.

$$\frac{dV}{dt} = \frac{I(1 \pm \text{tol}_I)}{C(1 \pm \text{tol}_C)}$$



Components:

- const. current source

charges
 capacitor → linear charge → ramp

comparator → ramp vs. V_{in} comparison

counter → counts only after reaching V_{in} → digital output

Pros:

- precision dependent on $\frac{dV}{dt} = \frac{I}{C}$ → I source, C component
- many bit ($n > 16$)

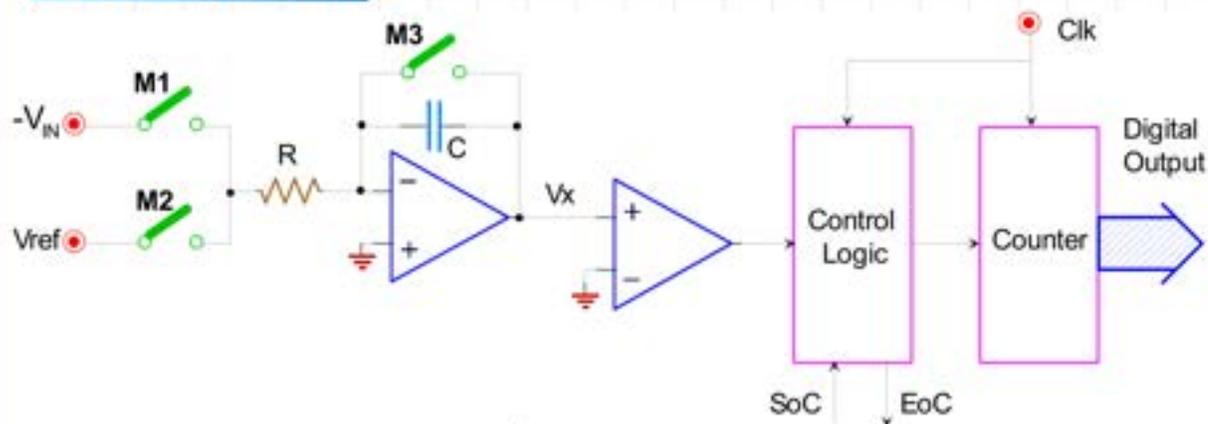
Cons:

- offset of comparator → makes ramp start from slightly
- slow (like staircase problems)
- irregular sampling comb
- too sensitive to tol of C, I source, CLK period

↳ low conversion accuracy

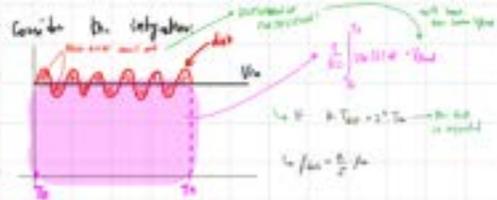
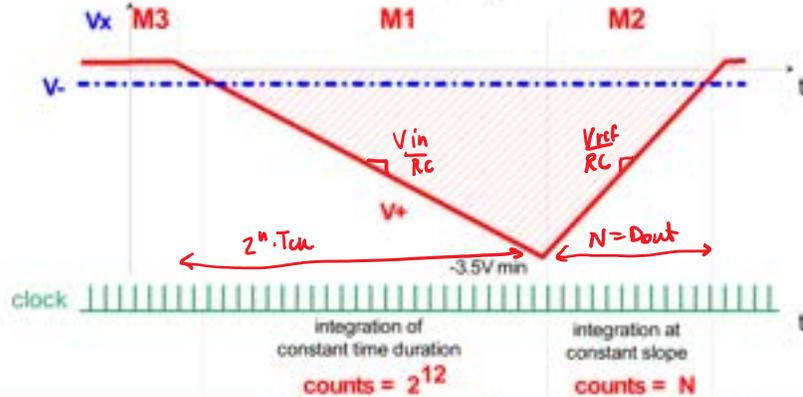
ADC: Dual slope ADC

Dual-slope ADC



$$\frac{V_{in}}{RC} \cdot 2^n T_{int} = \frac{V_{ref}}{RC} \cdot D_{out} \cdot T_{int}$$

$$D_{out} = \frac{V_{in}}{V_{ref}} \cdot 2^n$$



Components:

- integrating OpAmp $\xrightarrow{\text{Charge } M1}$ to obtain a ramp $\propto -V_{in}$ (integration for 2^n CLK pulses)
- $\xrightarrow{\text{discharge } M2}$ to obtain a ramp from $\int V_{ref}$ (const. slope) (So const slope)
- Counter \rightarrow count CLK pulses for integrations phases
- control logic \rightarrow switches control / SoC / EoC
- comparator \rightarrow detect when the value stored across C is 0 again $\rightarrow \bar{V}_{ref} = V_{in}$

Pros: precision independent of R and C (their toll.)

\hookrightarrow both charge/discharge ramps with the same $\tau = RC$

Disturbance rejection at freq = int. multiples of integration period

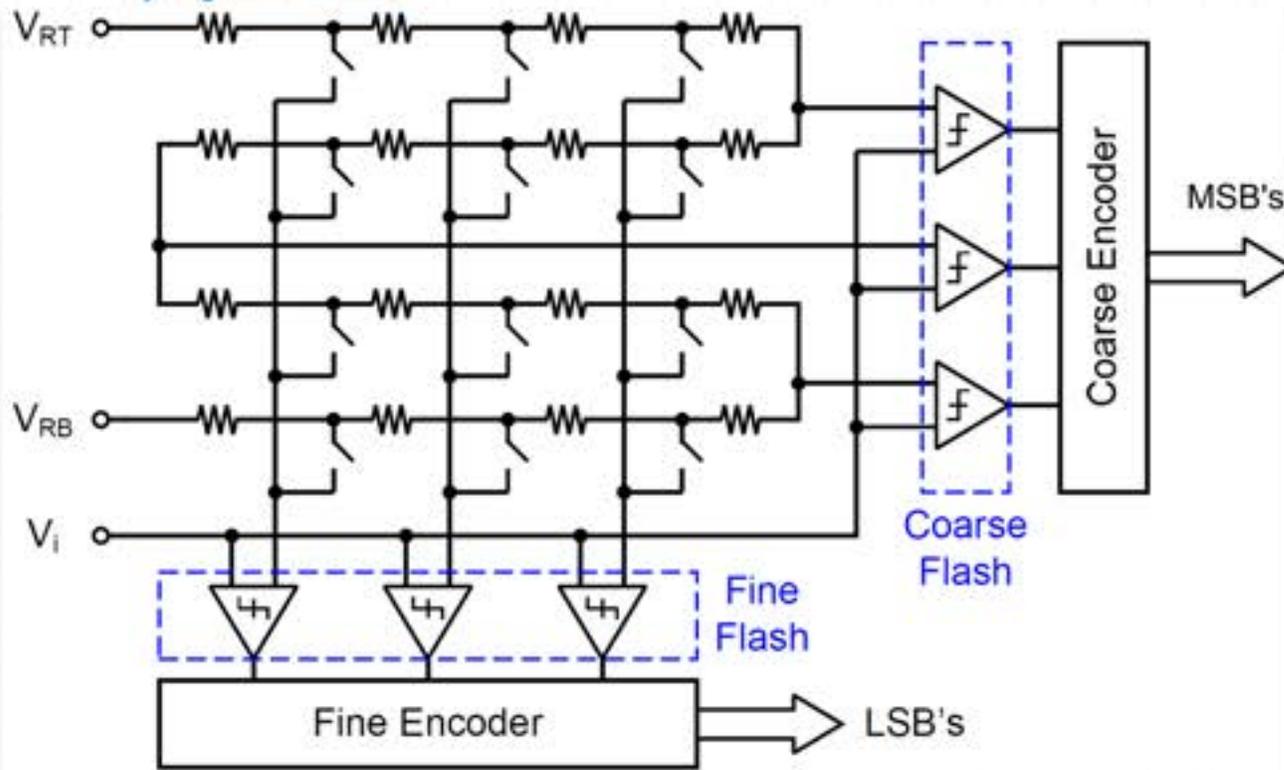
\hookrightarrow (NHR)

Normal Mode Rejection

Cons: High conversion time \rightarrow twice the one of single-slope

Advanced ADC: Subranging ADC

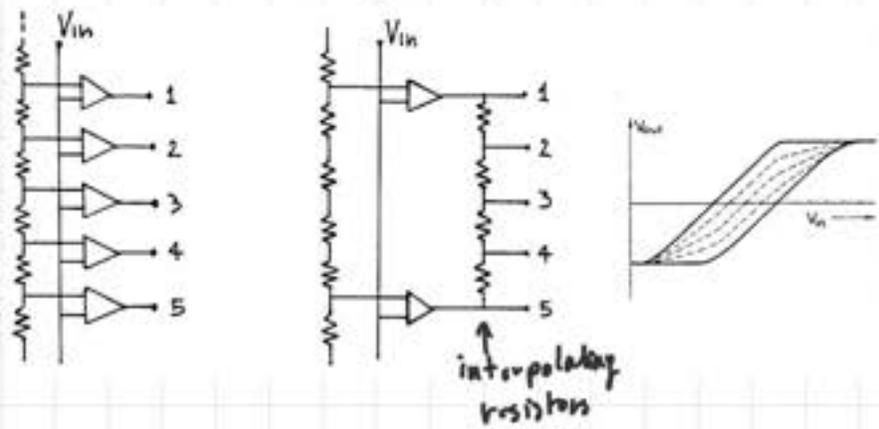
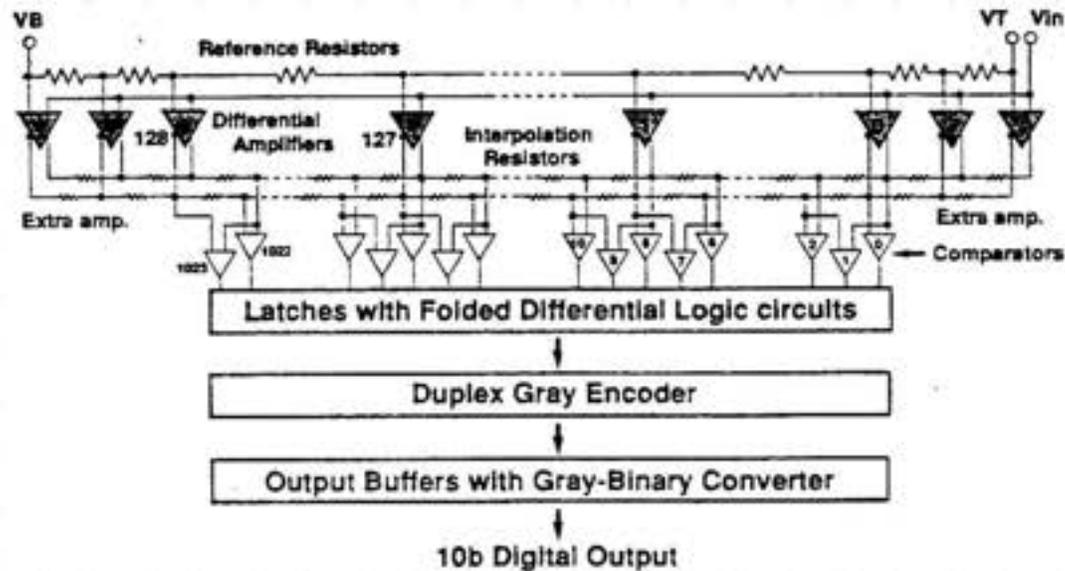
Subranging ADC



- Components:
- resistors → less for coarse conversion
→ create quantization levels
→ more for fine conv.
 - comparators → compare levels with V_{in}
 - encoders → (thermometric → binary)
- Pros:
- less waste of resources
 - when far from V_{in} → COARSE: less resolution
 - when near V_{in} → FINE: more resolution (small range)

Advanced ADC: Interpolation Flash ADC

Interpolation Flash-ADC



Components:

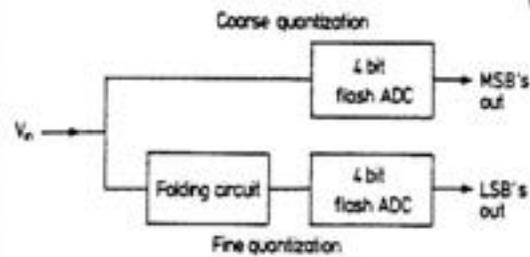
- resistors → reference
- interpolation → create levels from reference after comparison

- differential comparators → differential output
- latches with folded diff. logic circuit → sign of V_{out}
- Encoders

- Pros:
- use less comparators without losing levels
 - huge reduction of silicon area, power dissipation, input stray C
 - improved dynamic performances (settling time, speed...)

Advanced ADC: Folding Flash ADC

Folding Flash-ADC



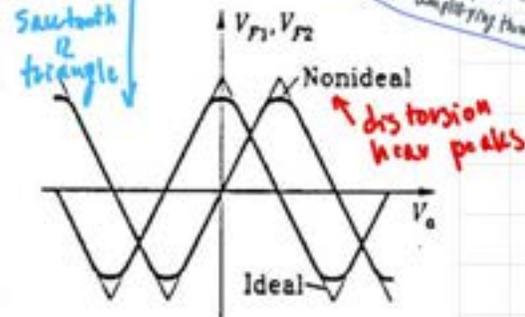
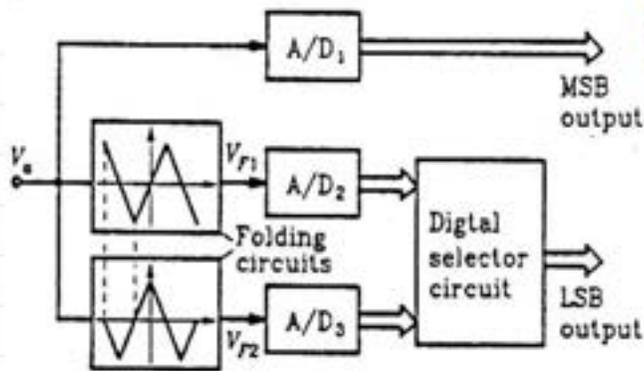
30 comparators instead of 256

Coarse quantization Subbit



Components: • Flash ADC → for coarse conversion (MSB) and partial fine conversion (LSB)

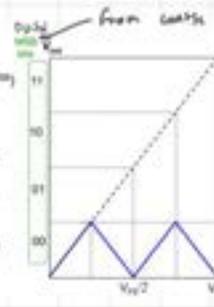
• Folding circuit → to allow fine conversion estimates the quantization error w.r.t the input signal



but actually sawtooth is triangle

Good we explore the error ranges amplifying them with fine conv.

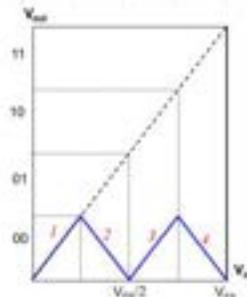
- Folding factor → number of folds (2^n)
- Folder maps input to smaller range
- MSB ADC determines which fold input is in
- LSB ADC determines position within fold
- Logic circuit combines LSB and MSB results



• How are folds generated?

- Fold 1 = $V_{in} - V_{ref}$
- Fold 2 = $V_{in} - V_{ref} - V_{ref}/2$
- Fold 3 = $V_{in} - V_{ref} - V_{ref}/2 - V_{ref}/2$
- Fold 4 = $V_{in} - V_{ref} - V_{ref}/2 - V_{ref}/2 - V_{ref}/2$

• Note: Sign change every other fold + reference shift



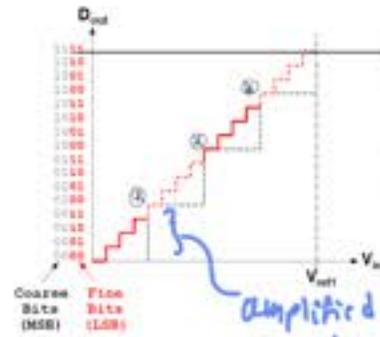
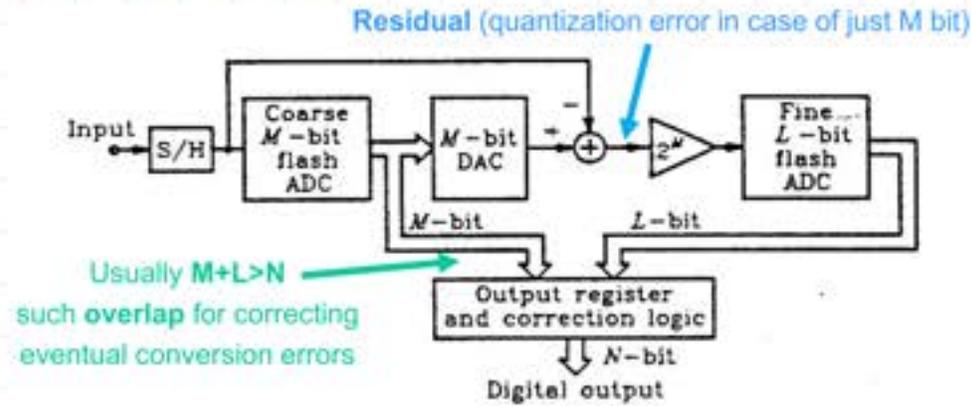
Send the error subranges to fine conv. (after an ampl.)

Pros: • Folding reduces the comparator number by a folding factor F (number of preamps stays the same)

Cons: • folding signals can suffer from distortion/non idealities on folding edges → use just zero-crossing

Advanced ADC: Half Flash ADC

Half-flash ADC



Components:

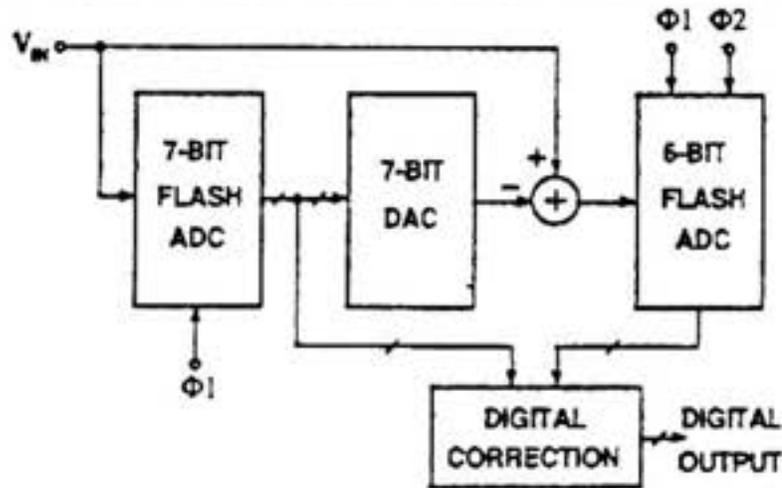
- low bit flash converters → for conversion steps

- DAC → convert first round of MSB to an A signal to feed then the Fine ADC (accuracy of at least N total ADC)

- Amplifiers → to amplify the residual coming from M bit coarse ADC quantization

sum and correction logic → for correction use $M+L > N$

↑ Total bit



Pros:

- minimize area occupation and power consumption

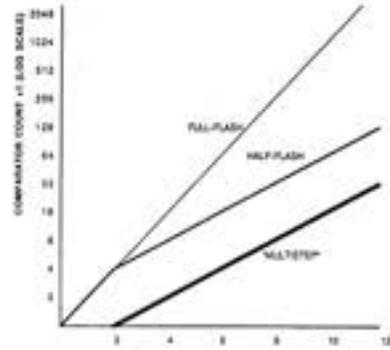
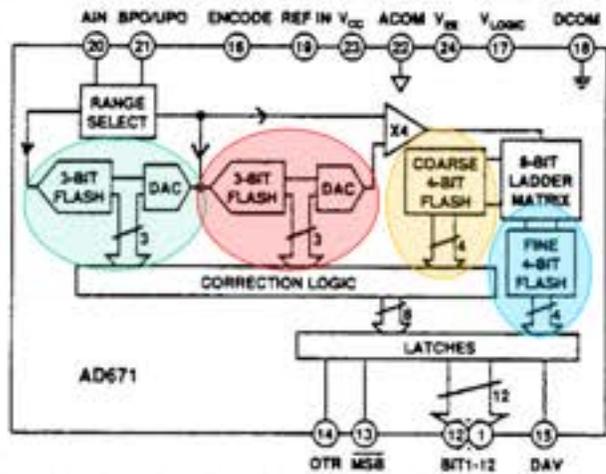
Cons:

- slow conversion time

overlapping bits correct any conversion edges →

Advanced ADC: Multistep ADC

• Multistep ADC



Components: • Same as previous flash solutions
↳ but not only made of 2 stages
↳ more stages in CASCADE

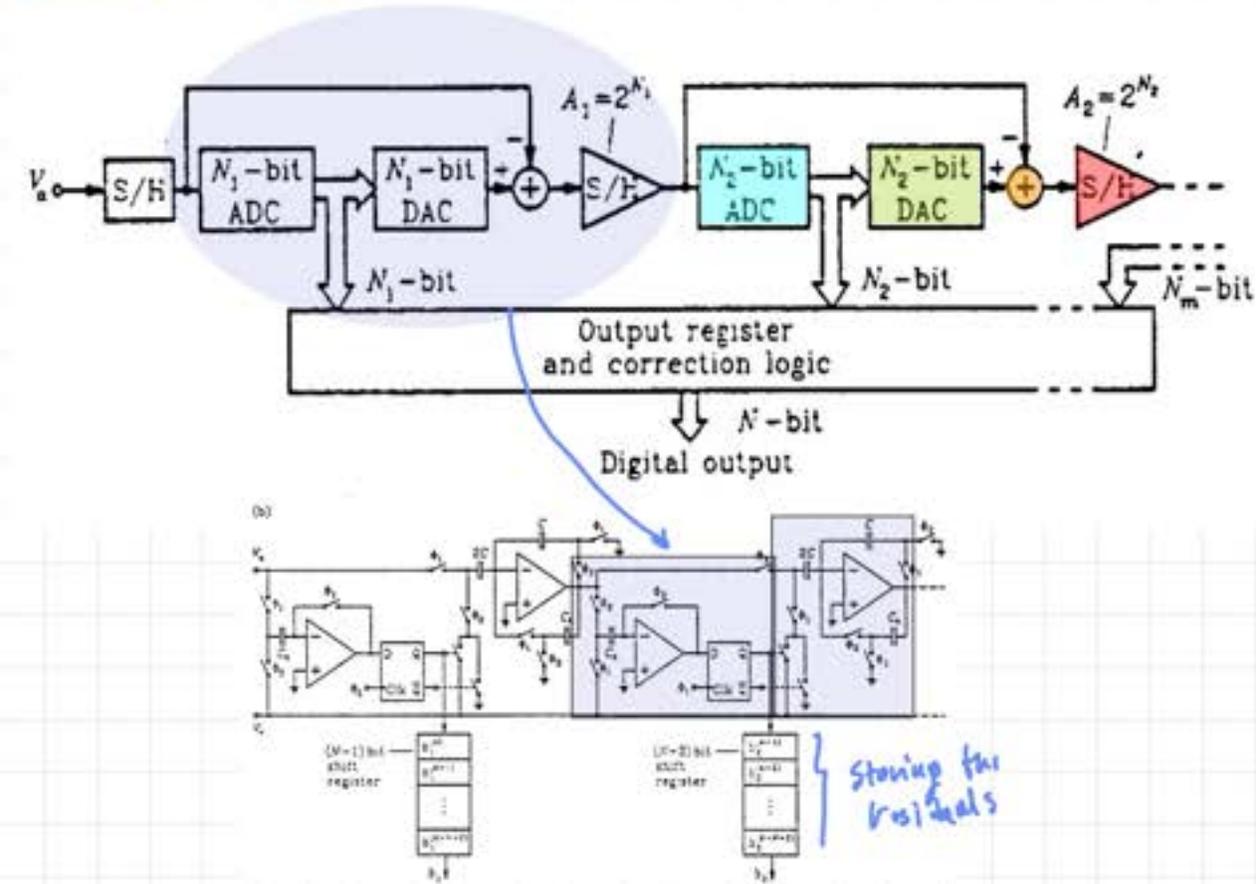
← Pros: • less comparators → (low area occupation)

Cons: • conversion time \propto # stages → slow!

← better to use pipelined

Advanced ADC: Pipelined ADC

Pipelined ADC



Components: • same of half flash/multistep stages

• + S/H → to put before every stage → we hold the residual value, so the stage can directly proceed with another conversion

parallel-pipelined processing

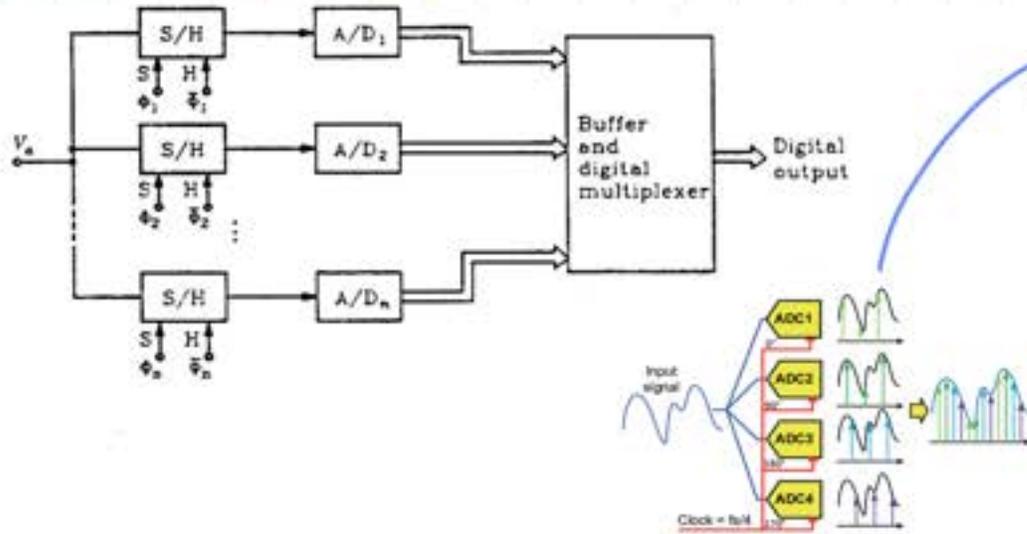
Pros: • fast conversion time
 ↳ w/ half-flash/multistep improves of a factor equal to # m stages of pipeline

• low area occupation and power consumption

Cons: • compromises b/w speed and accuracy
 ↳ $m \uparrow$ conversion time ↓ accuracy ↓ (noise increases stage after stage)

Advanced ADC: Time-interleaved ADC

Time-interleaved ADC



Components: • ADCs → put in parallel

• S/H → put before every ADC
Channels operate in sequence

Pros: • # stages faster w/rt single channel
↳ achieve conversion speed not possible with single converters

Cons: • different channel behaviour, non regularity of sampling intervals

due to systematic errors b/w channels

↓
create spurious freq. components

Offsets: $\text{sample times at multiples of } T_c$

Gains: $\text{sample times at } T_c/2, 3T_c/4, 5T_c/4, \dots$

Sampling time: $\text{sample times at intervals increasing with } n$